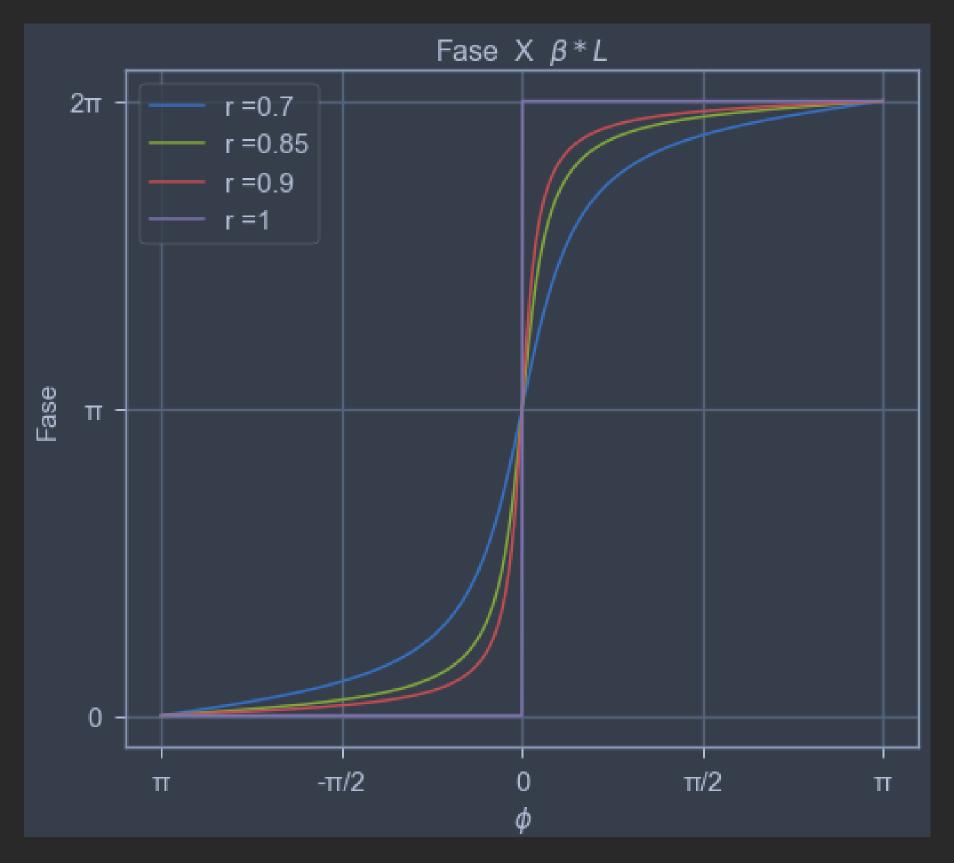
DESIGN ANEL DE RESSONANCIA

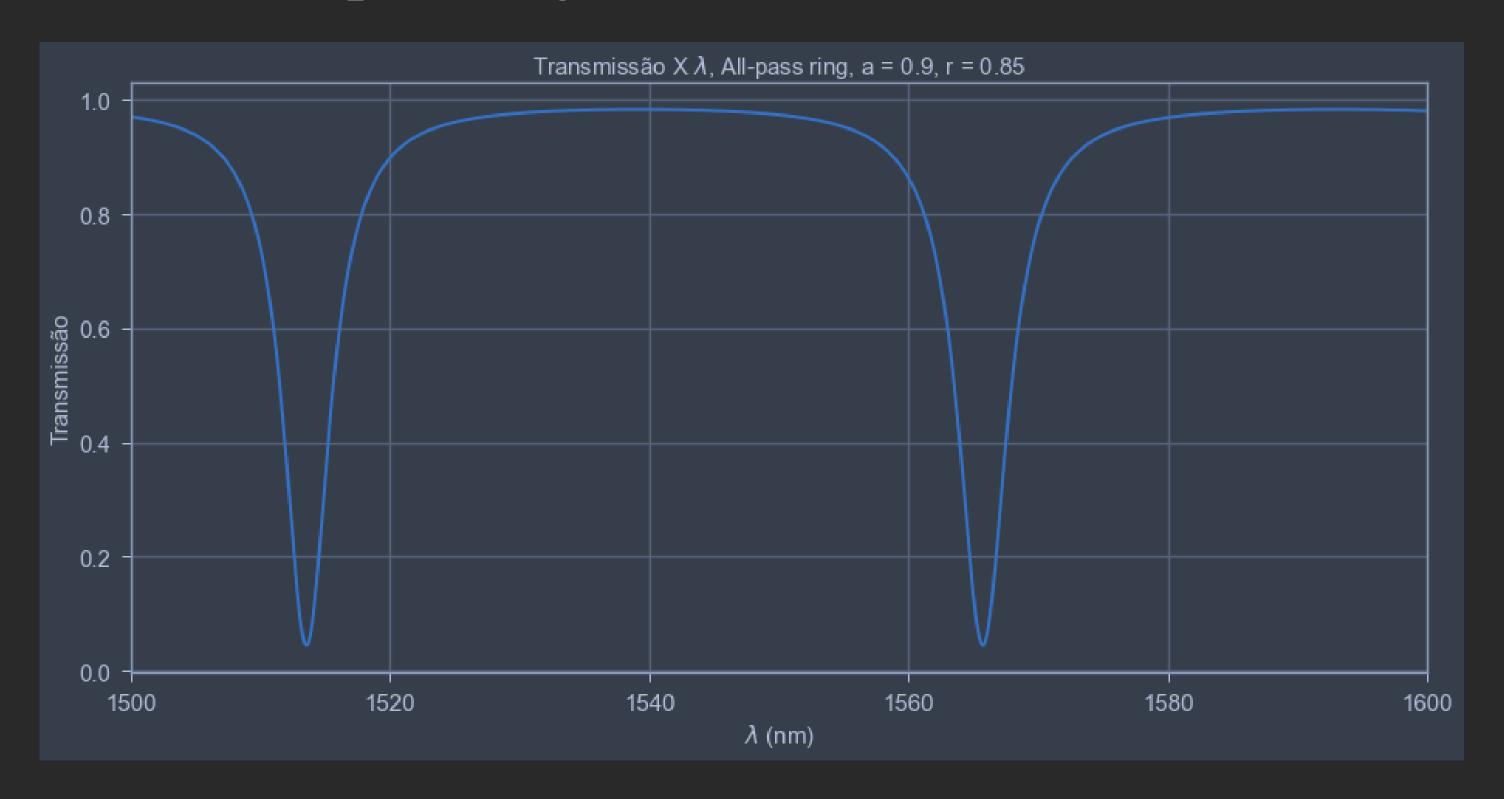
SEMANA 1 E 2

ESTUDO DE REFERENCIAS

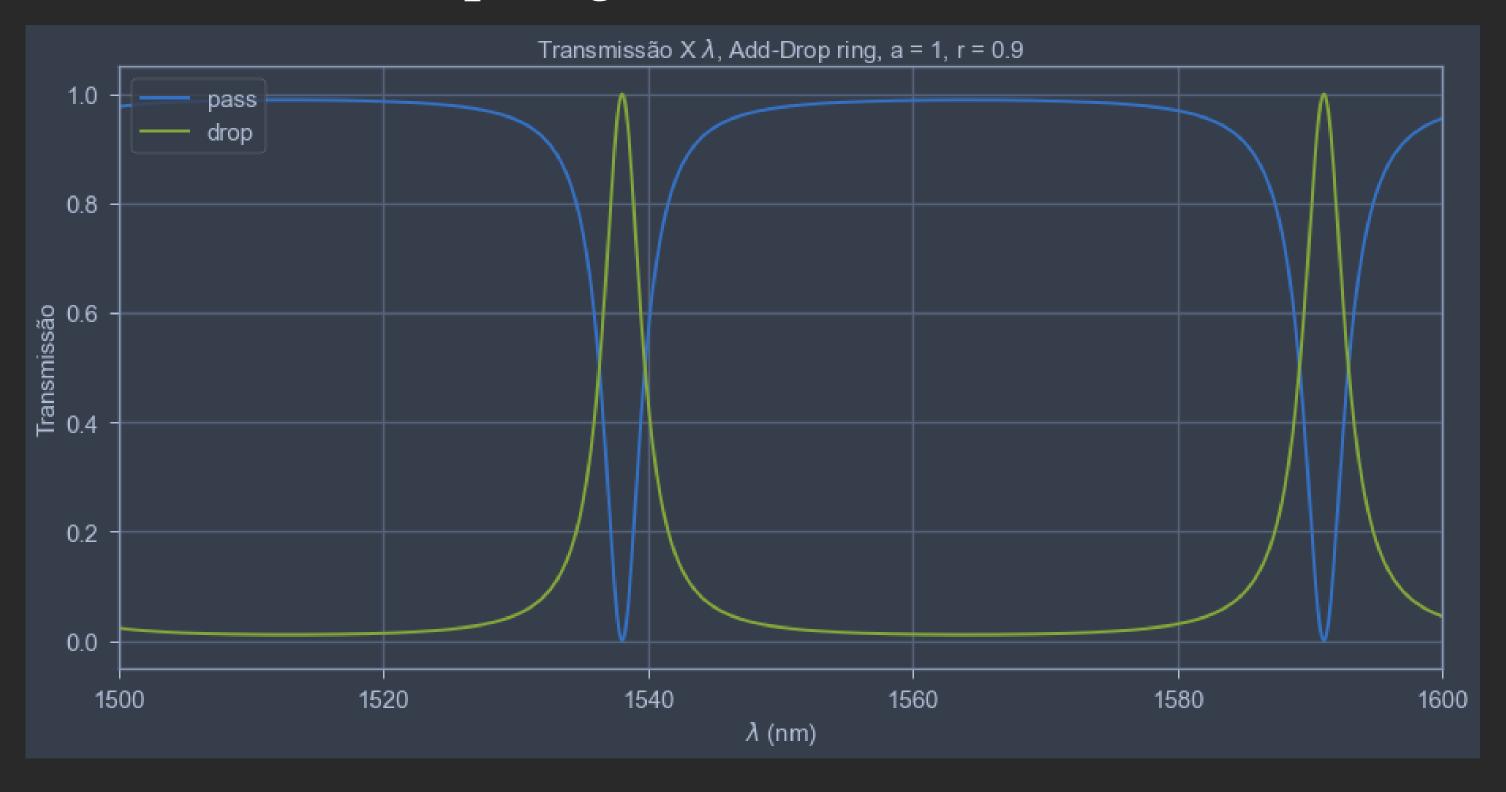
GRÁFICOS TEÓRICOS



GRÁFICOS TEÓRICOS Transmissão All pass ring



GRÁFICOS TEÓRICOS Transmissão Add-drop ring



Especificações

FSR = 27.7 nm

MWHW = 0.88 nm

SOI in SiO2

Guia: 0.45/0.22 um

gap = 150 nm

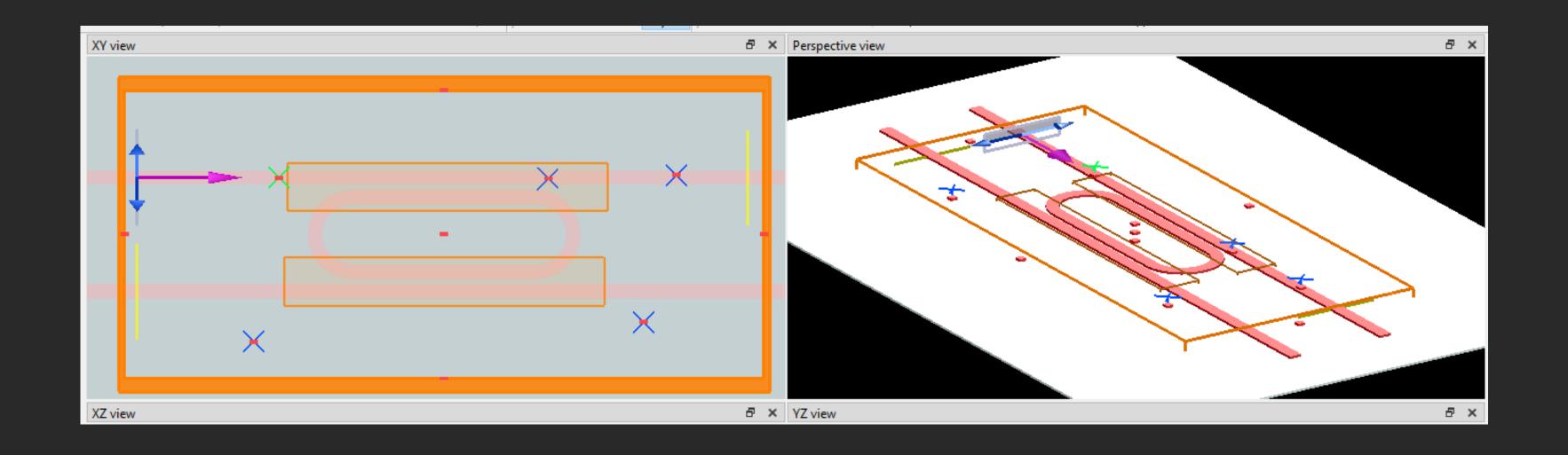
Valores Teóricos

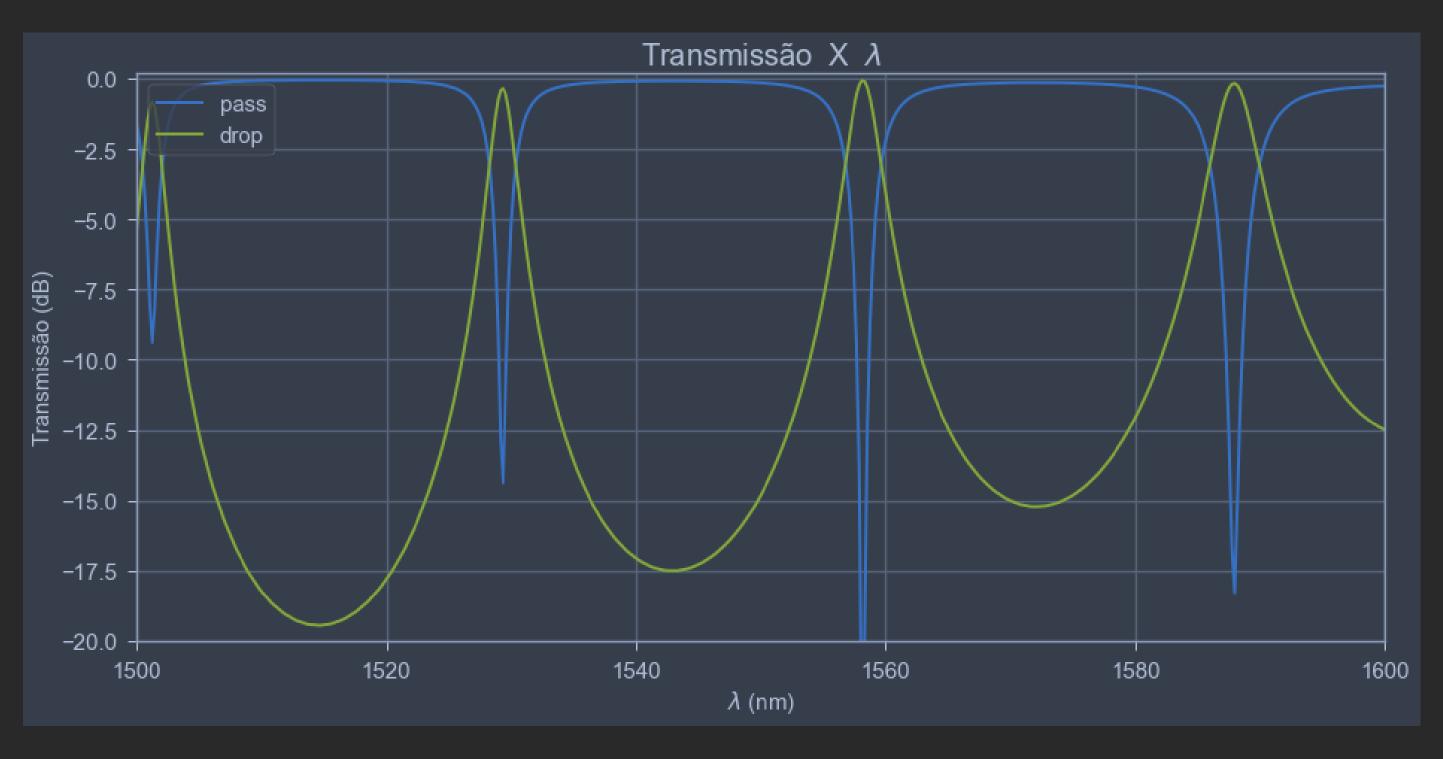
Comprimento total = 18.85 um

Comprimento de acoplamento = 5.74 um

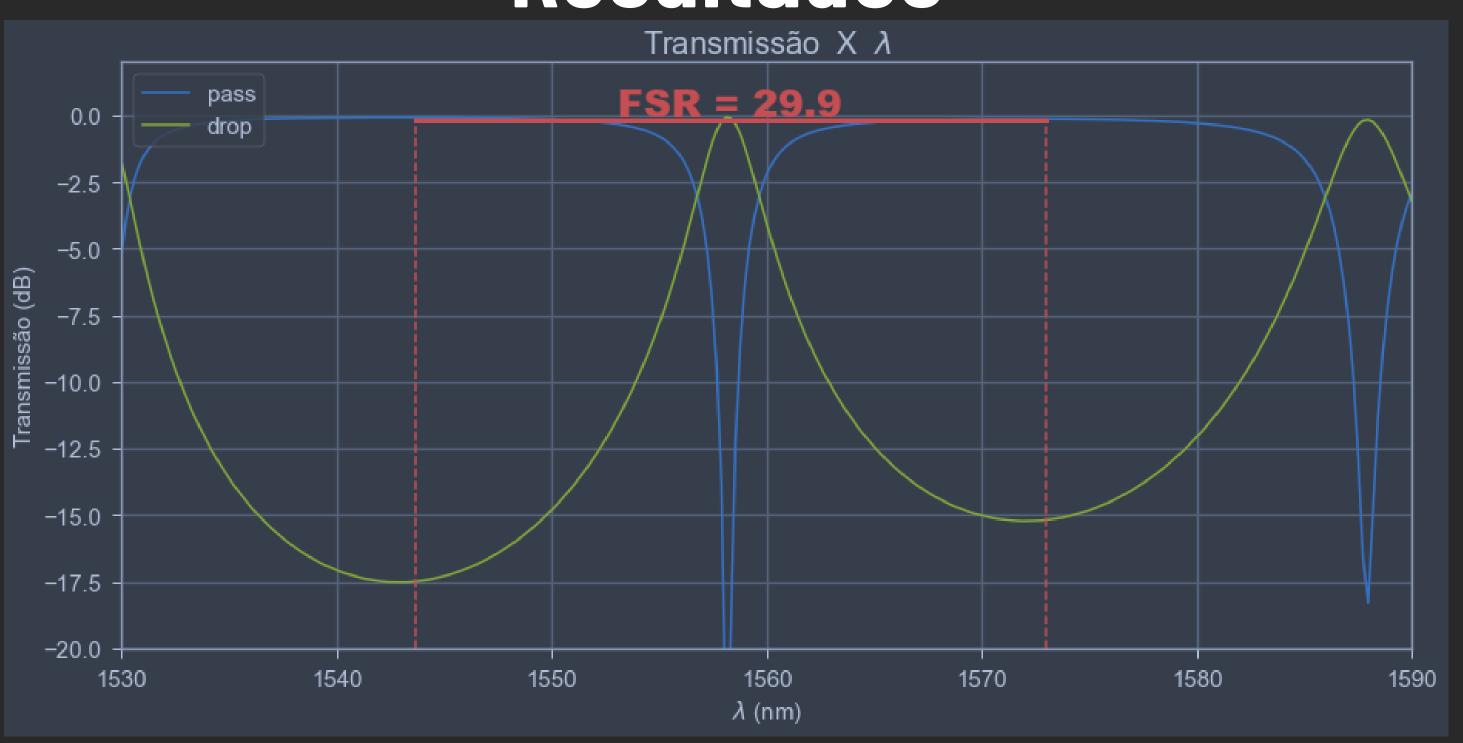
Raio = 1.17 um

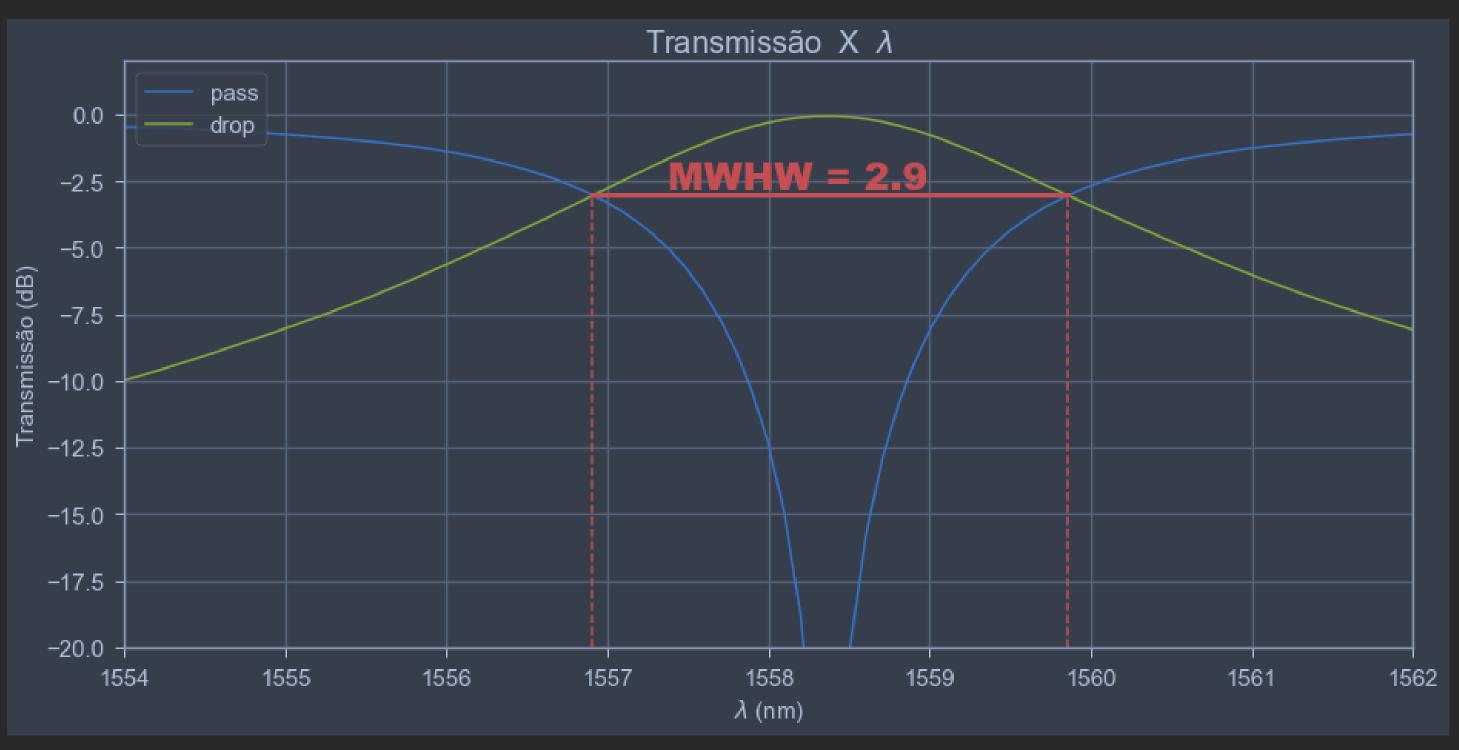
DESIGN DE UM ANEL DE RESSONÂNCIA Simulação



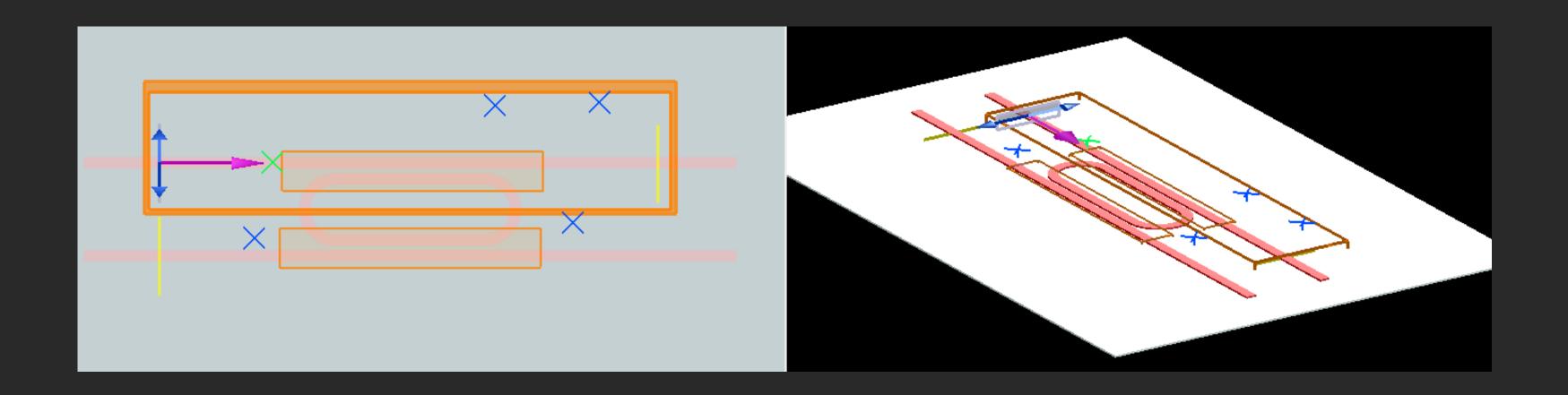








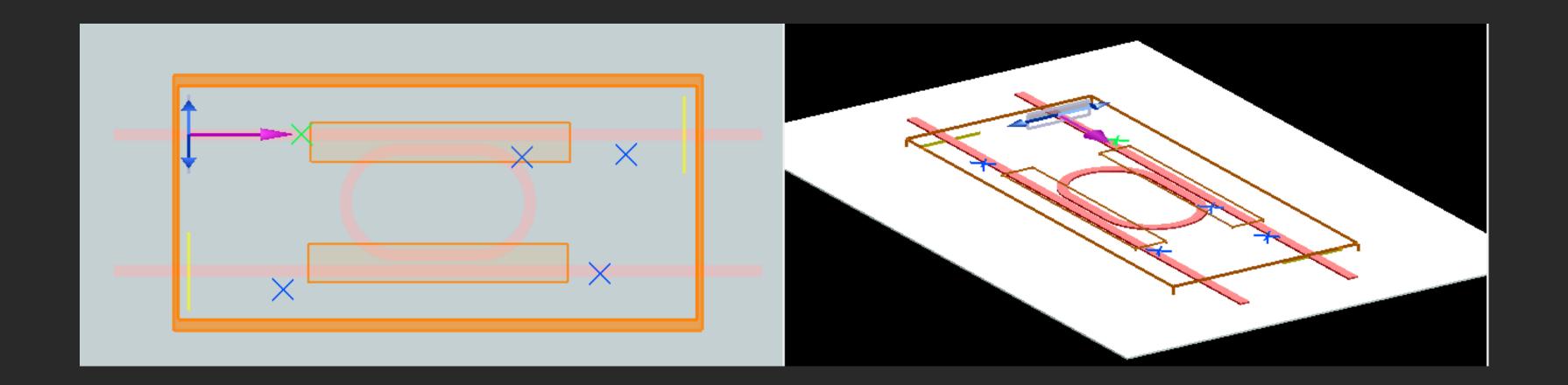
DESIGN DE UM ANEL DE RESSONÂNCIA Sweep comprimento de acoplamento

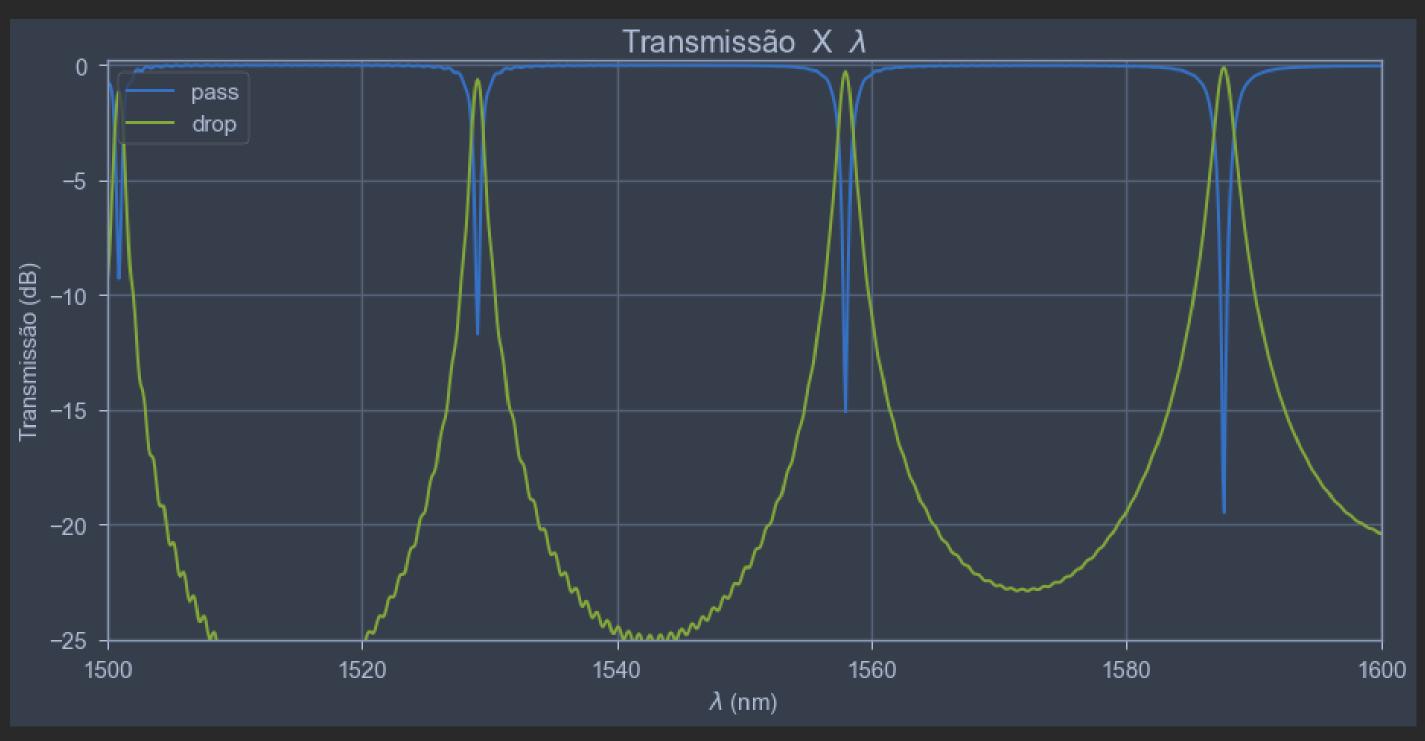


DESIGN DE UM ANEL DE RESSONÂNCIA Sweep comprimento de acoplamento

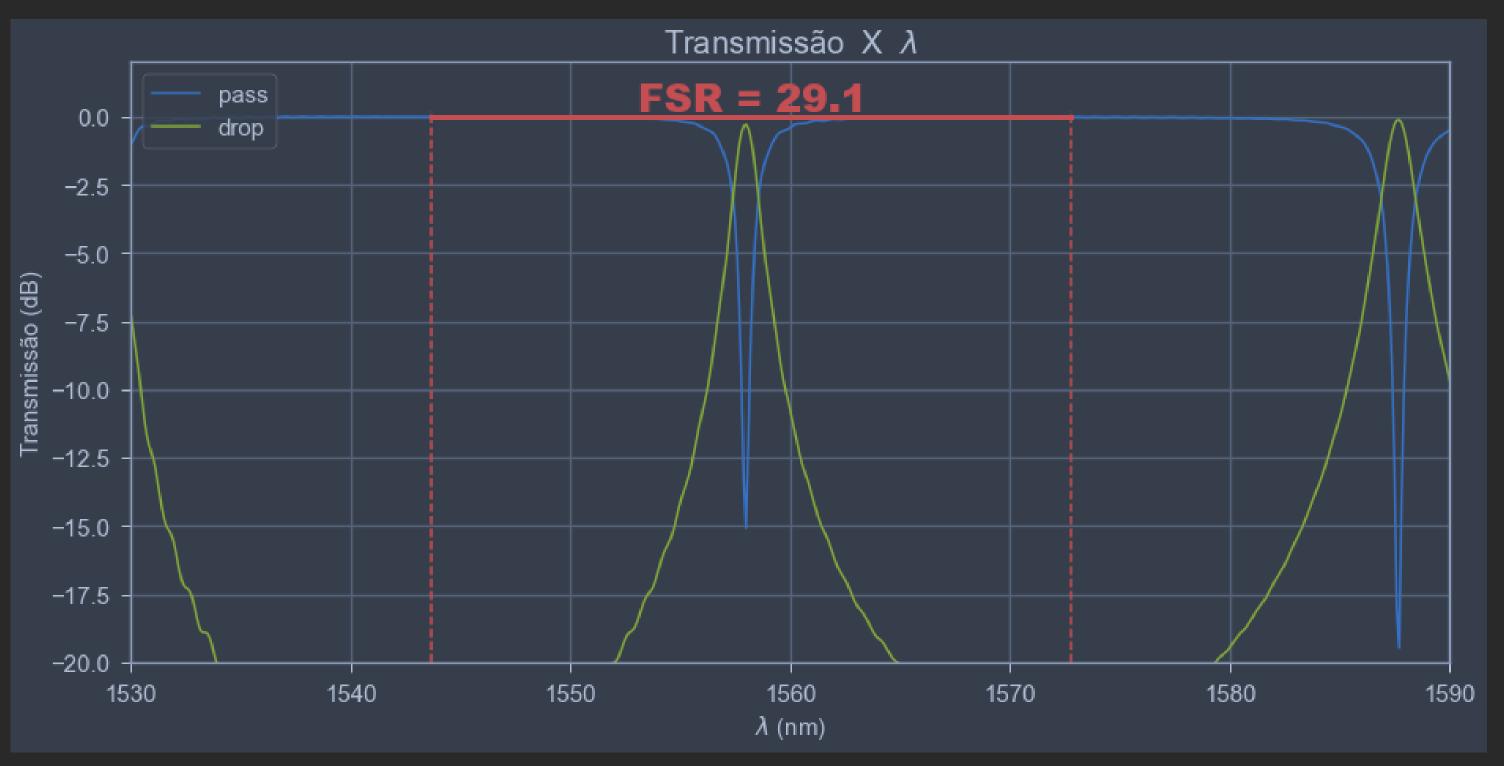


DESIGN DE UM ANEL DE RESSONÂNCIA Usando L acoplamento = 3.0.5 um











SEMANA 3

DESIGN ANEL BANDA C

Especificações
Centrado na banda C
FSR = 0.8 nm
MWHW = 0.2 nm

Guia: 0.45/0.22 um

SOI in SiO2

gap = 150 nm

Valores Teóricos

Comprimento total = 650.82 um

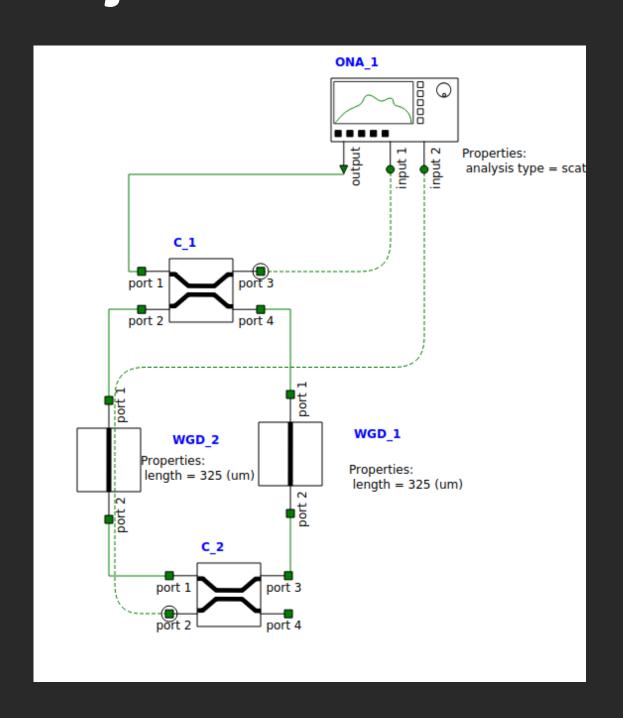
Comprimento de acoplamento = 15.13 um

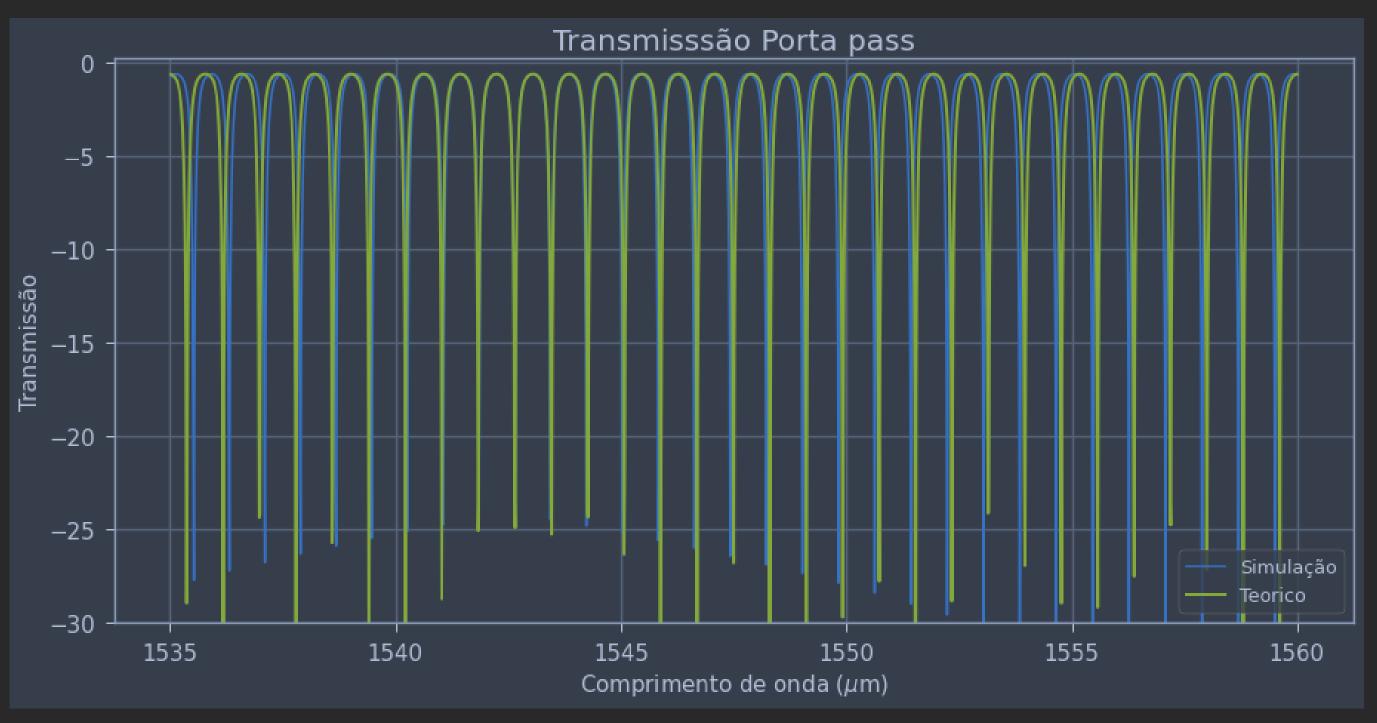
Raio = 98.76 um

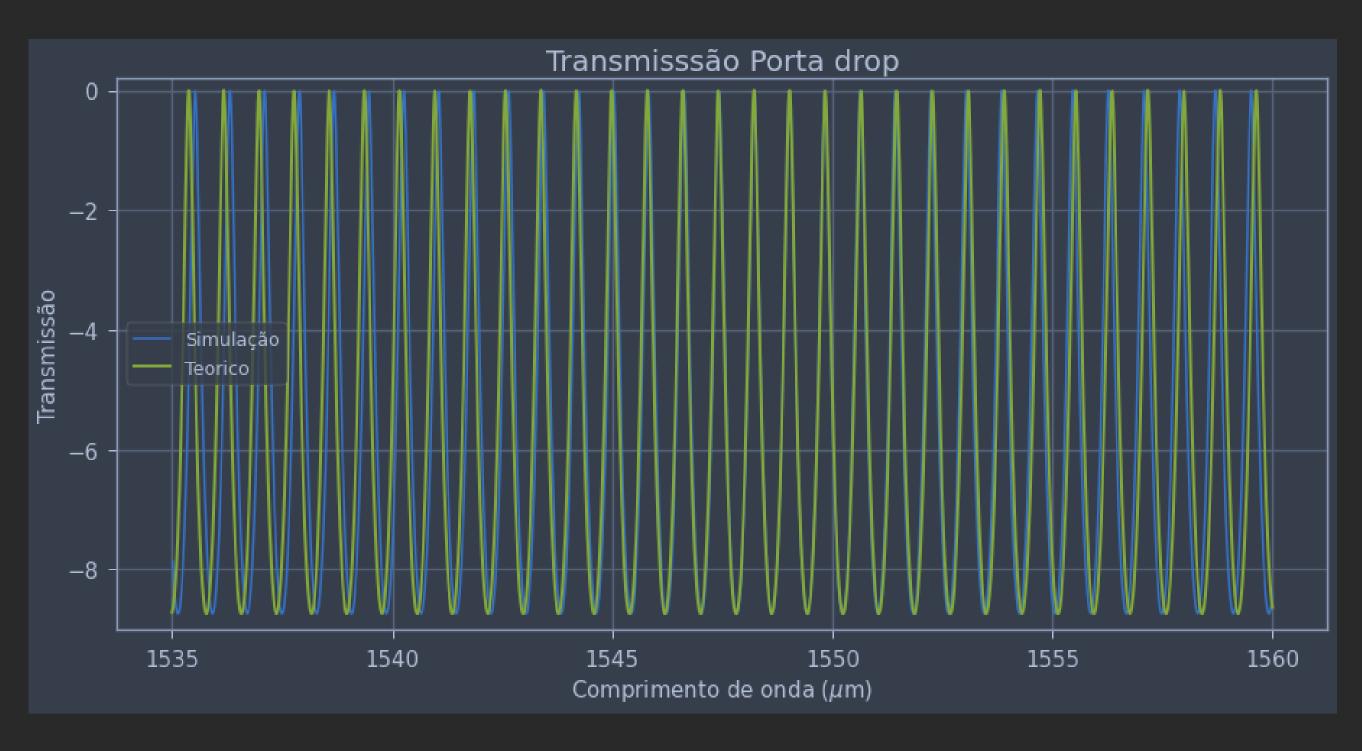
Q factor = 7749

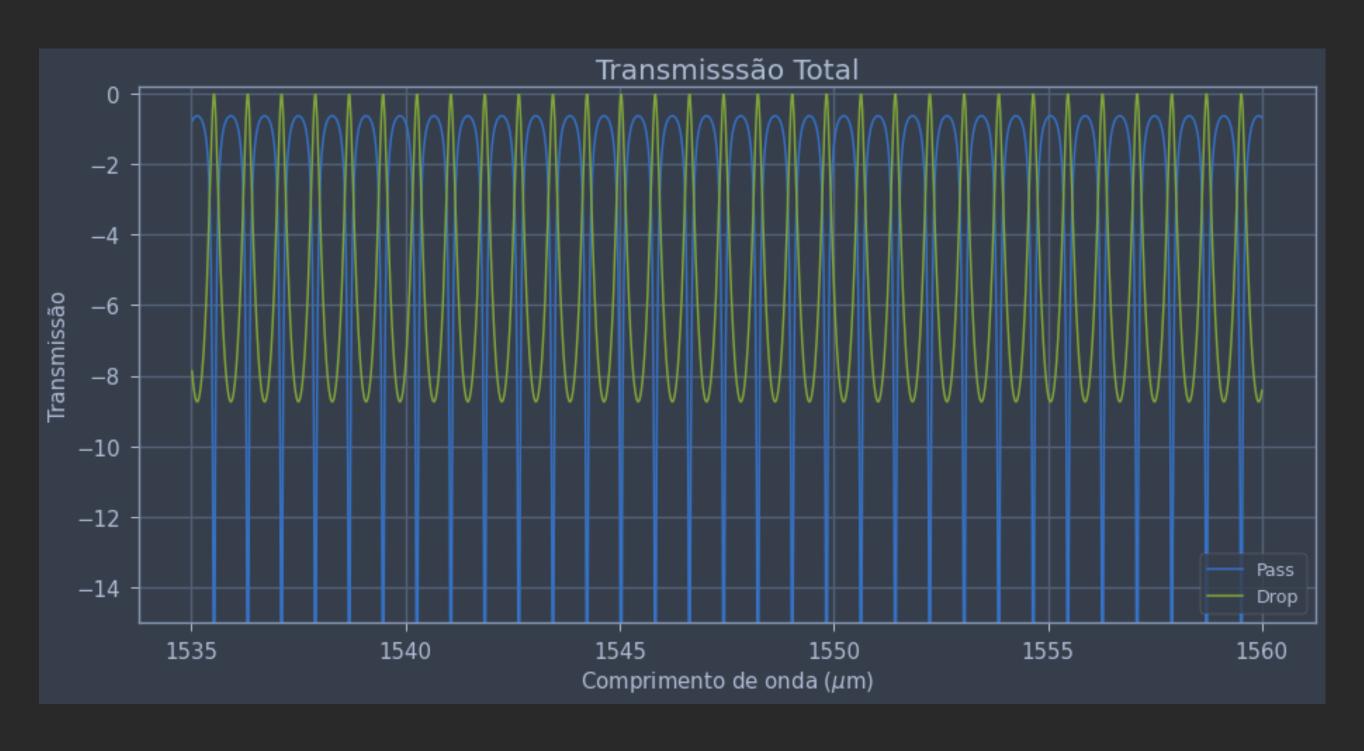
Finesse = 4

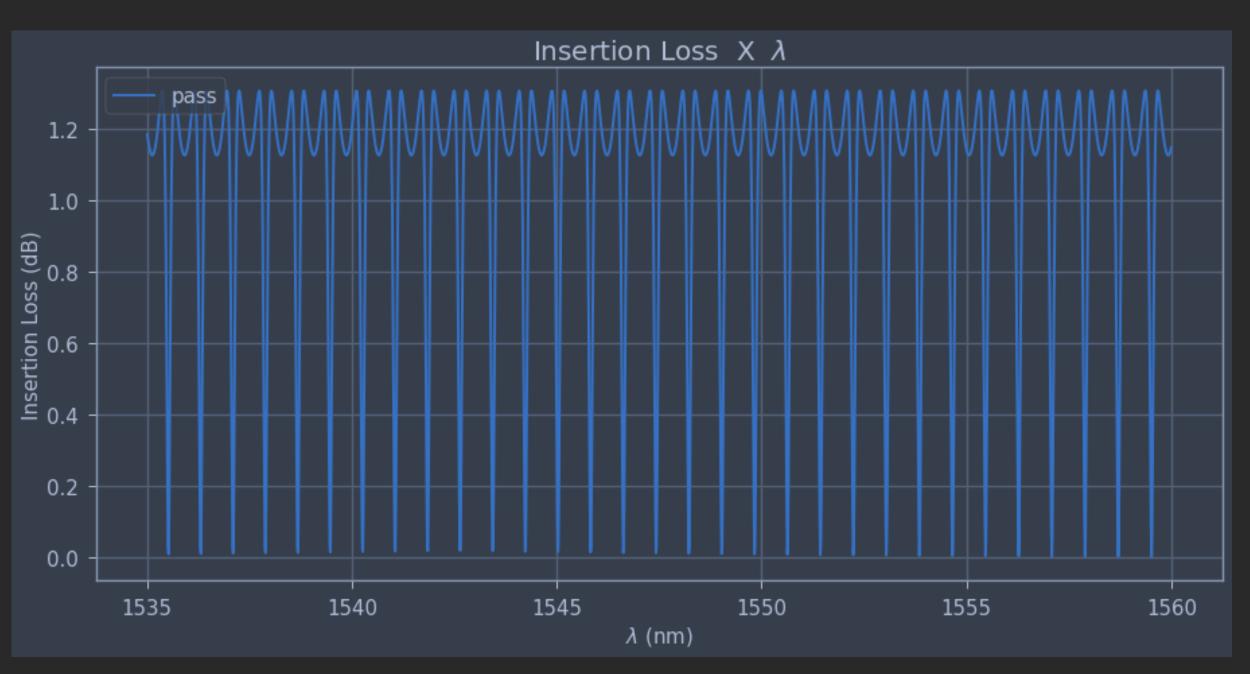
DESIGN DE UM ANEL DE RESSONÂNCIA Simulação no Interconect

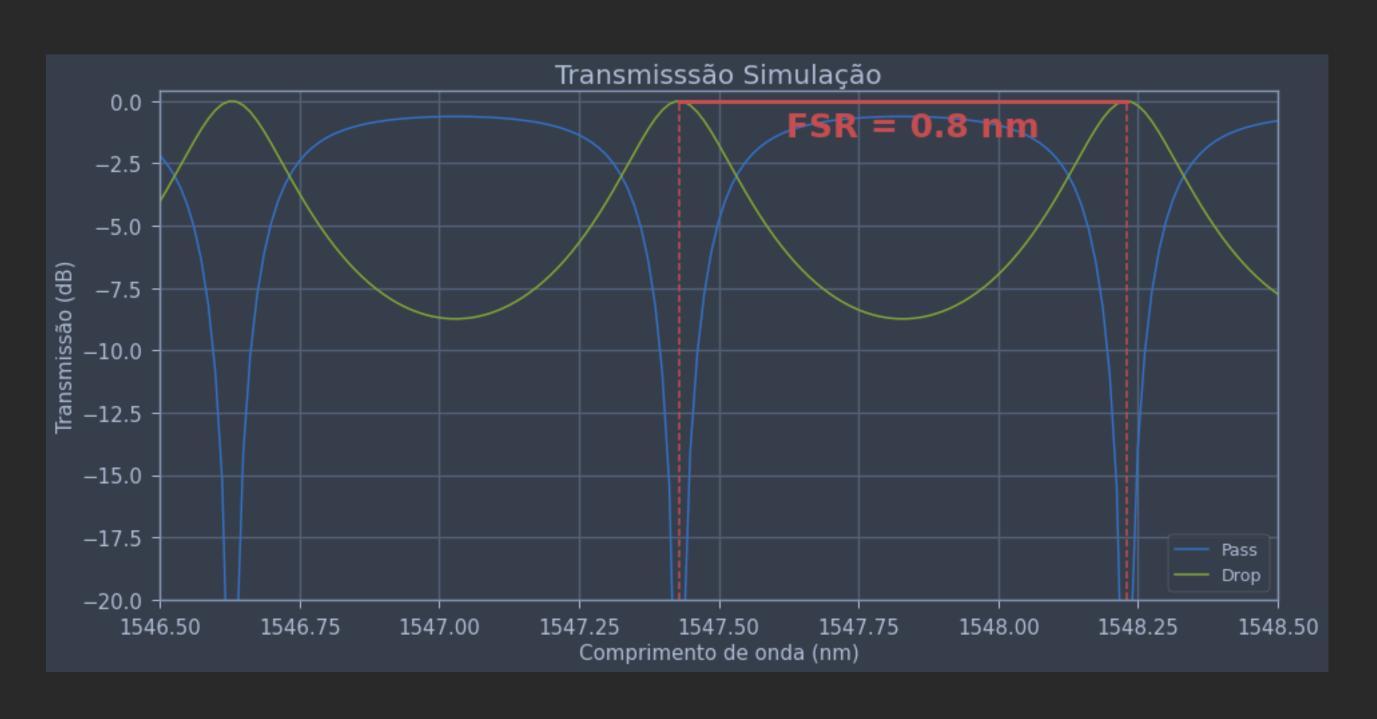


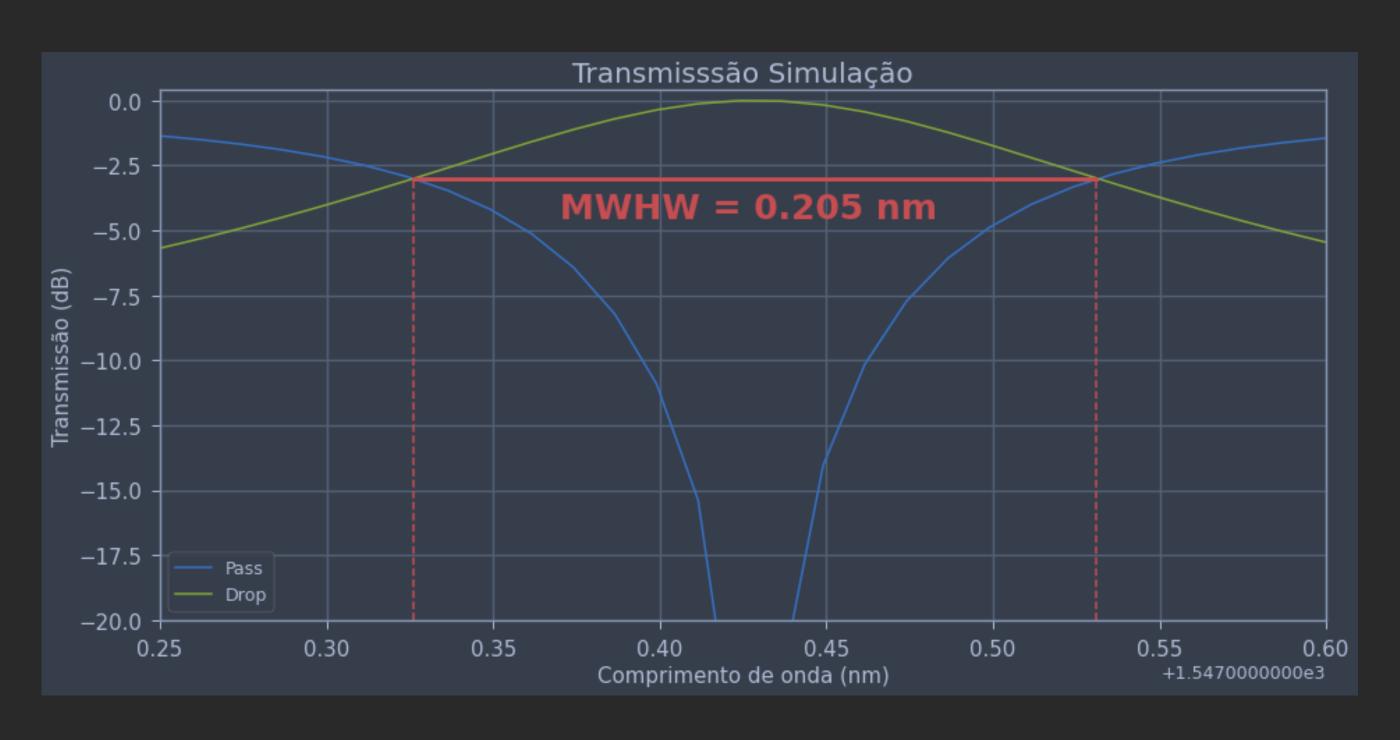


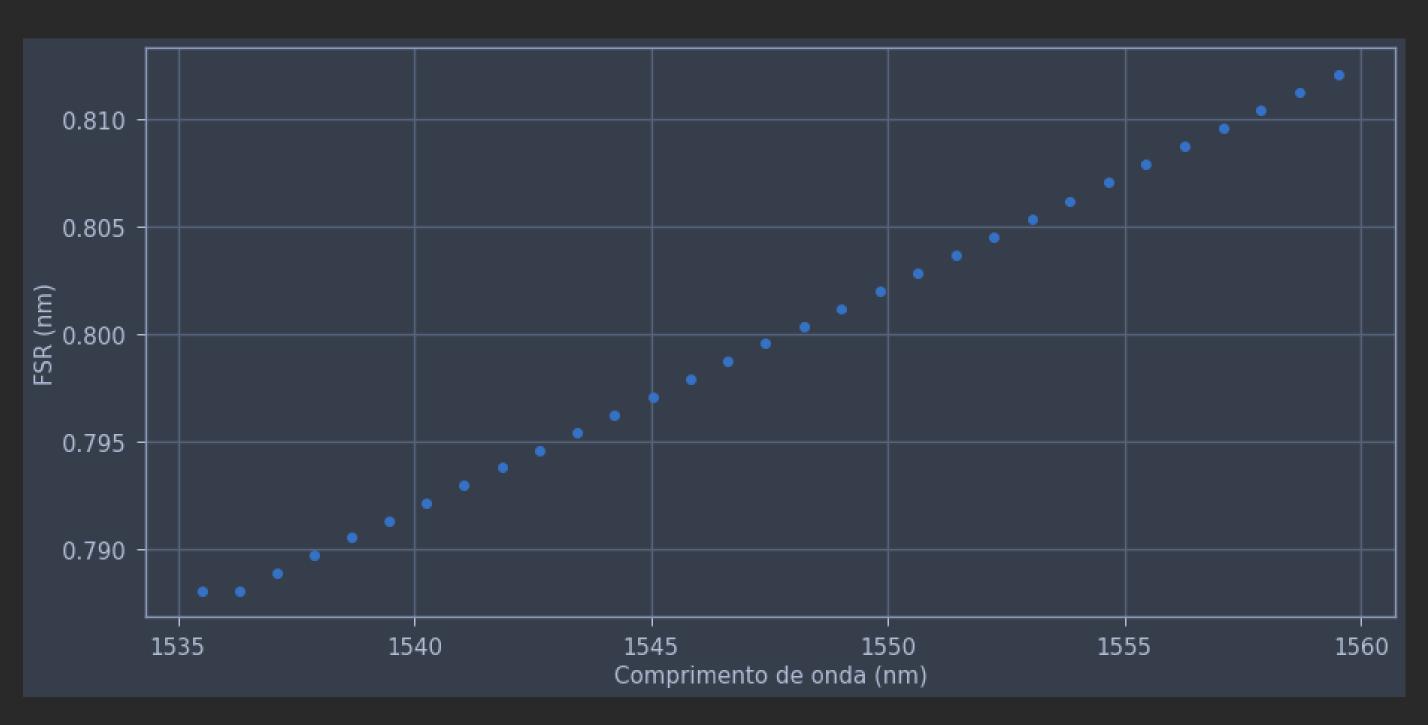


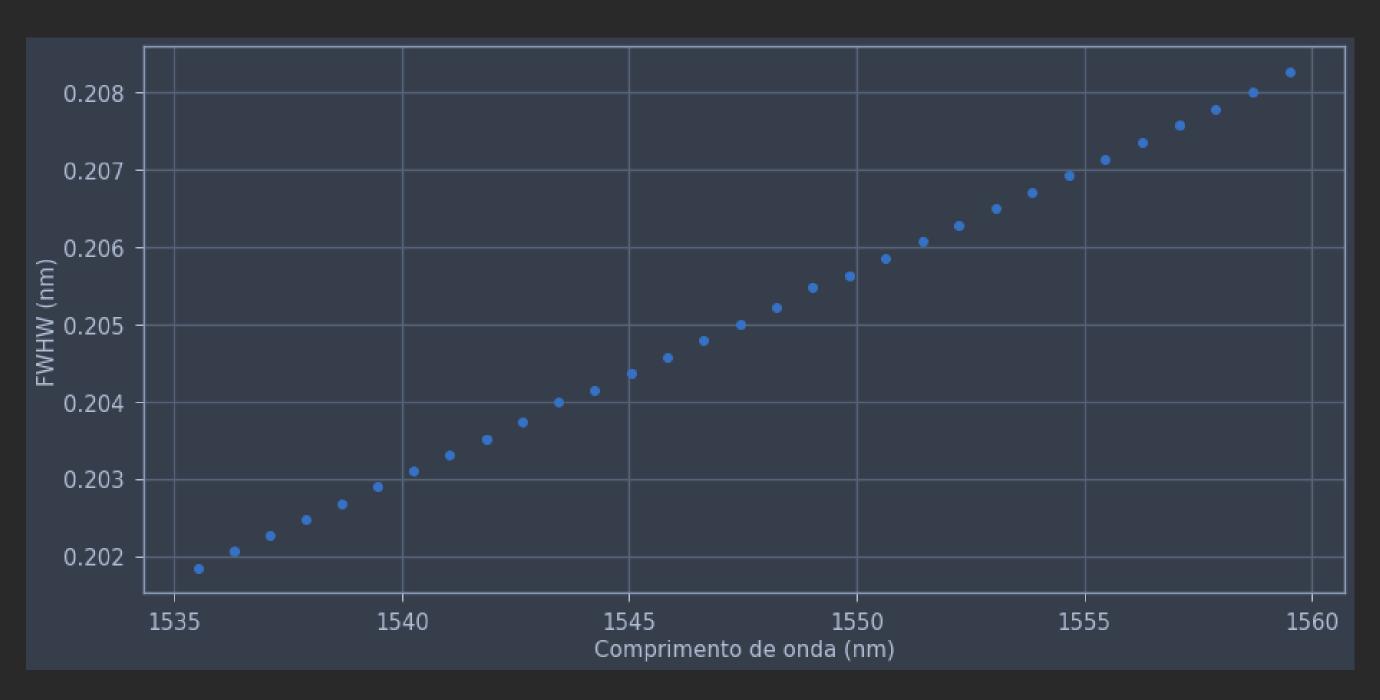


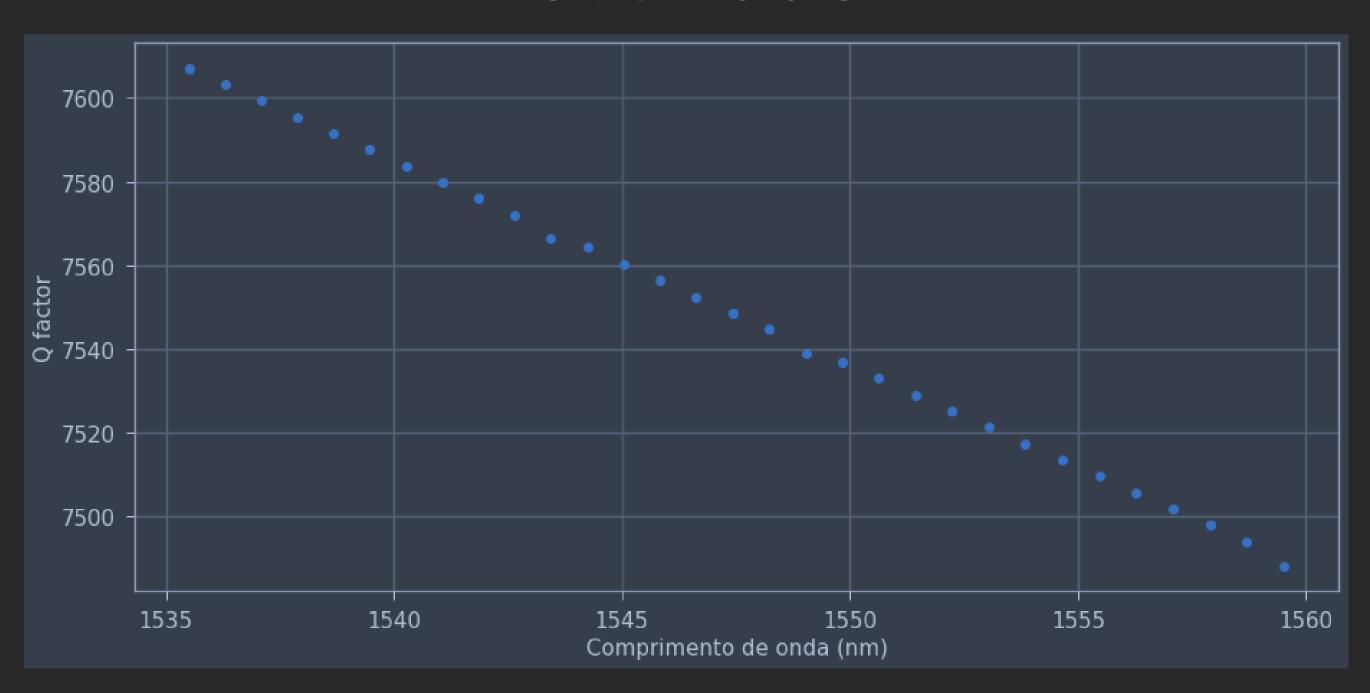


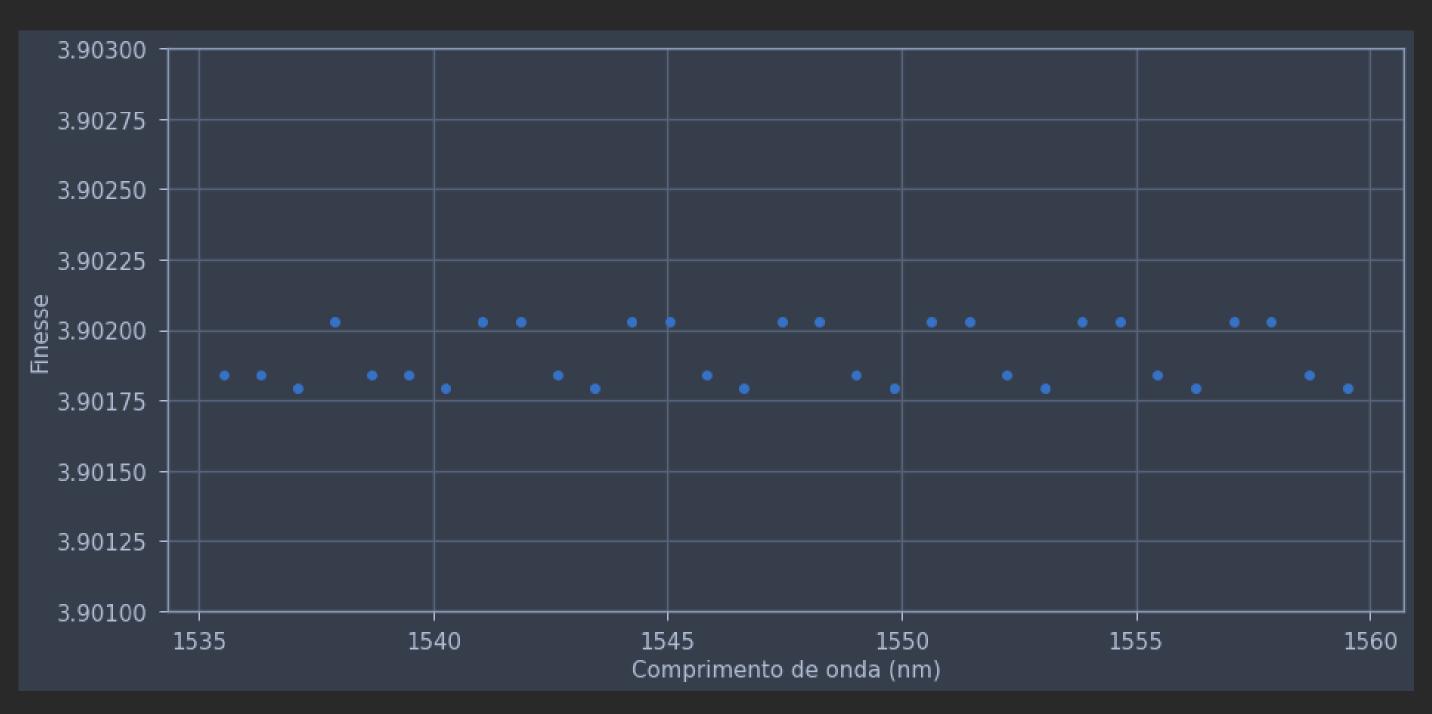












Analise do acoplamento

Solver usado: EME





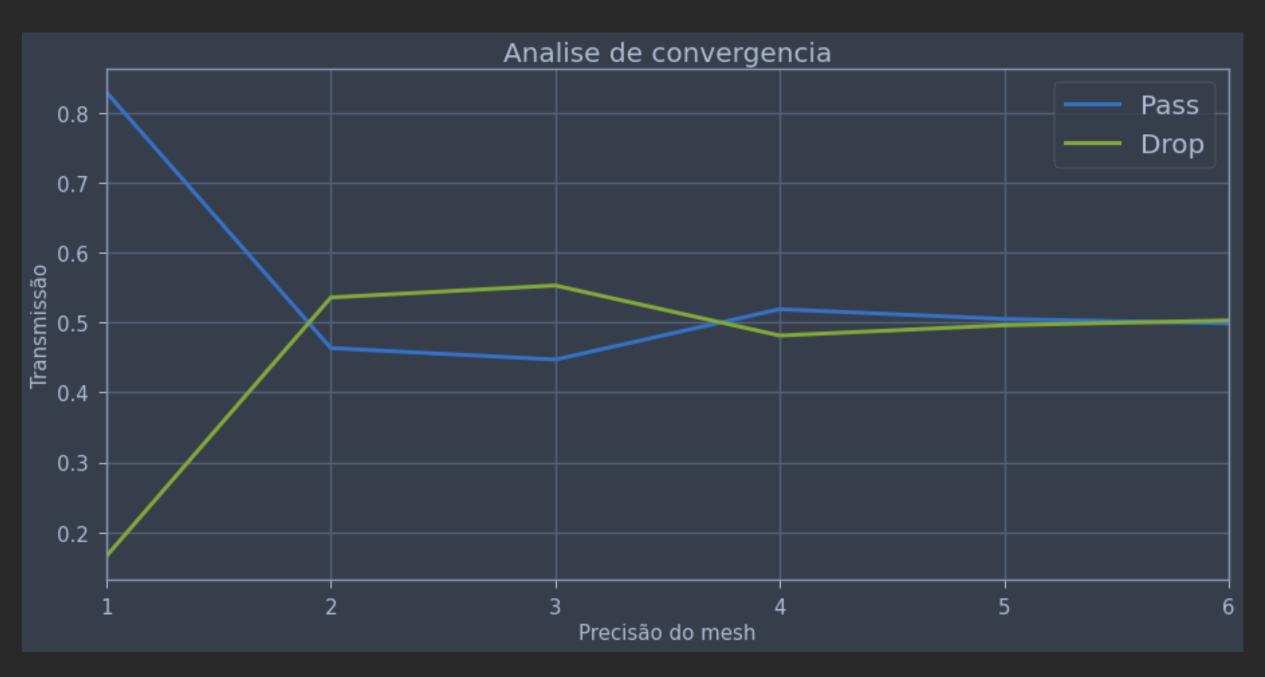
SEMANA 4

Simulações no FDTD

DESIGN DE UM ANEL DE RESSONÂNCIA Simulação dos componentes



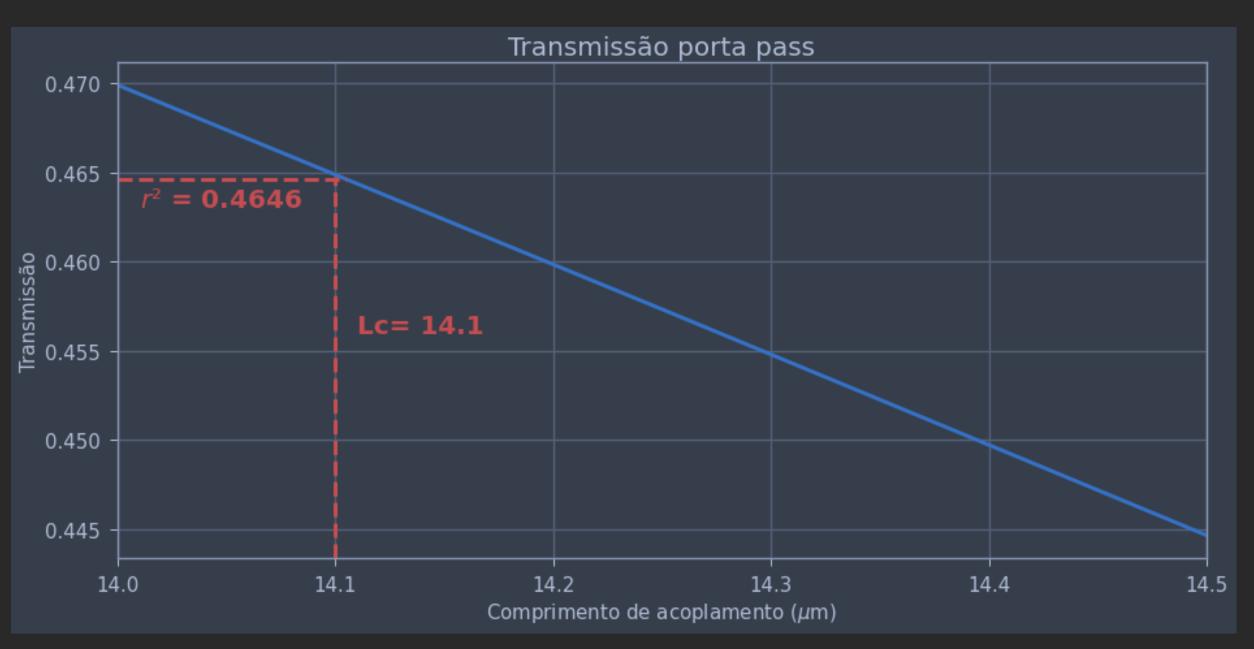
Analise de convergência

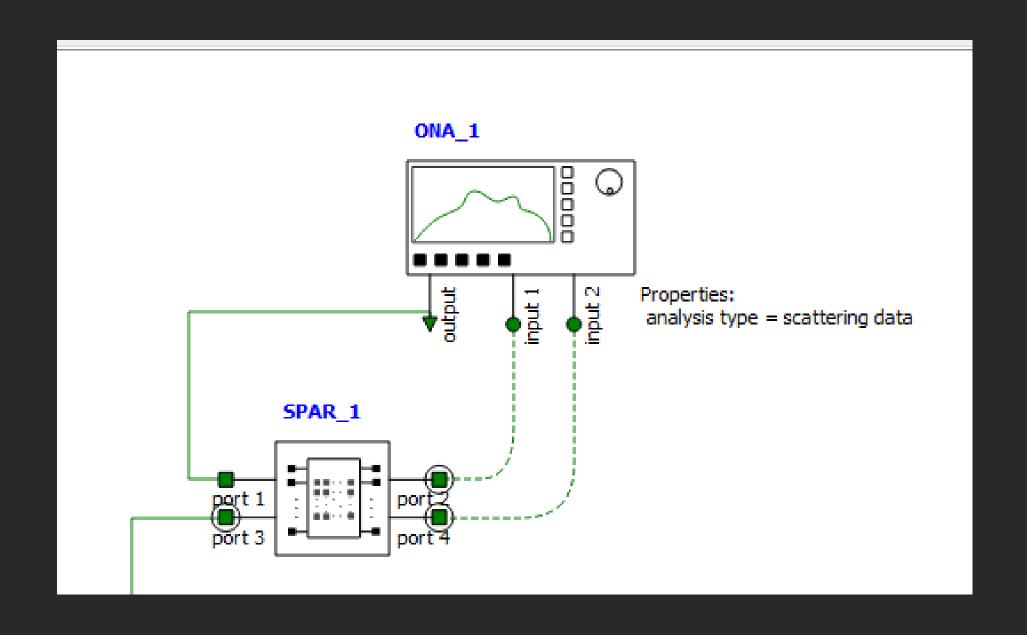


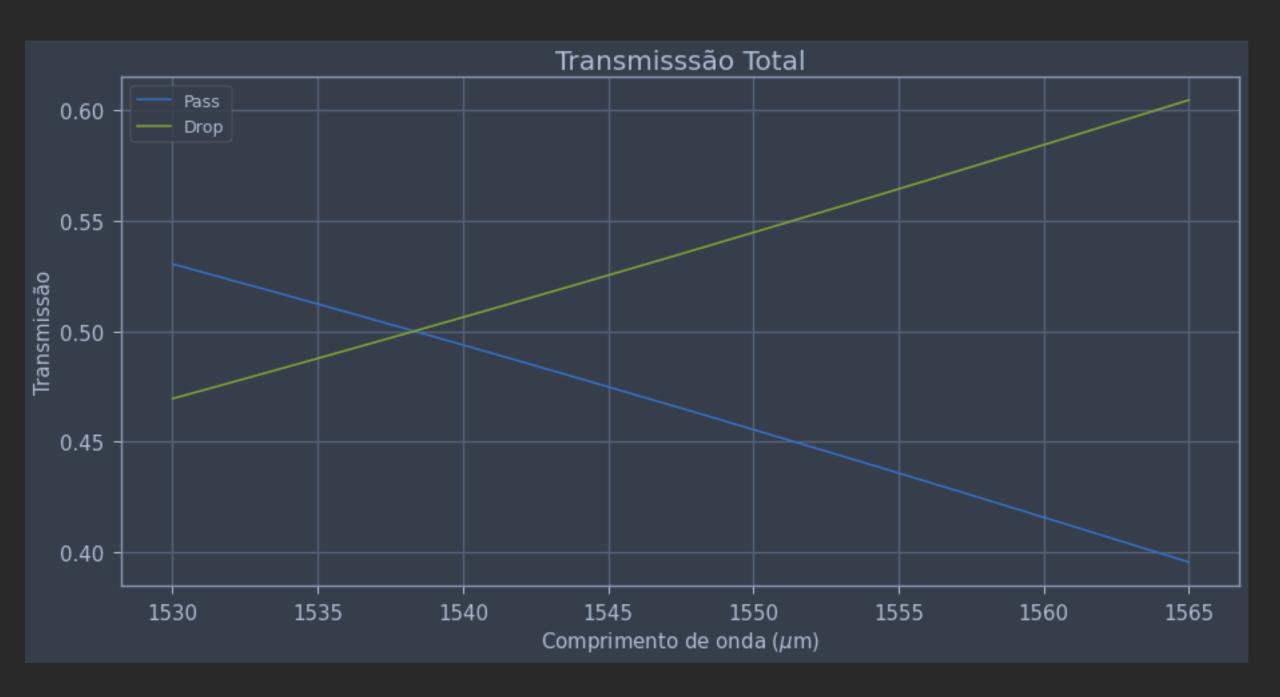
Analise do acoplamento



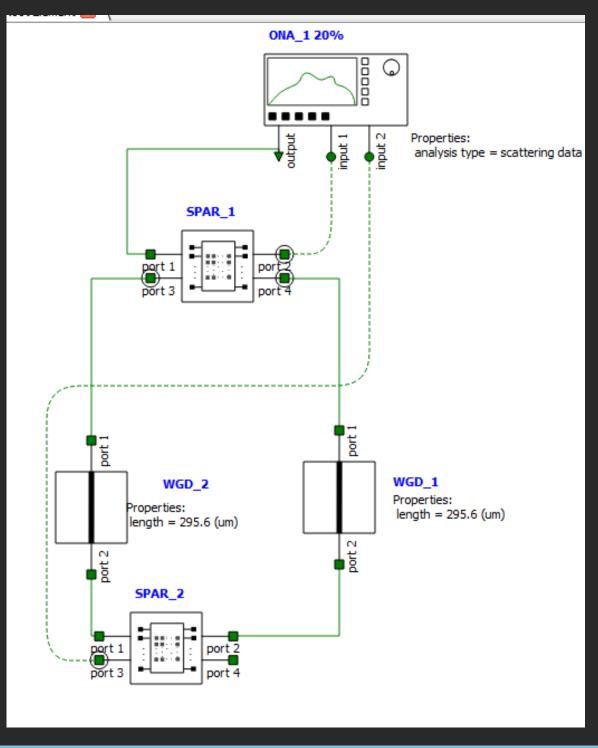
Analise do acoplamento

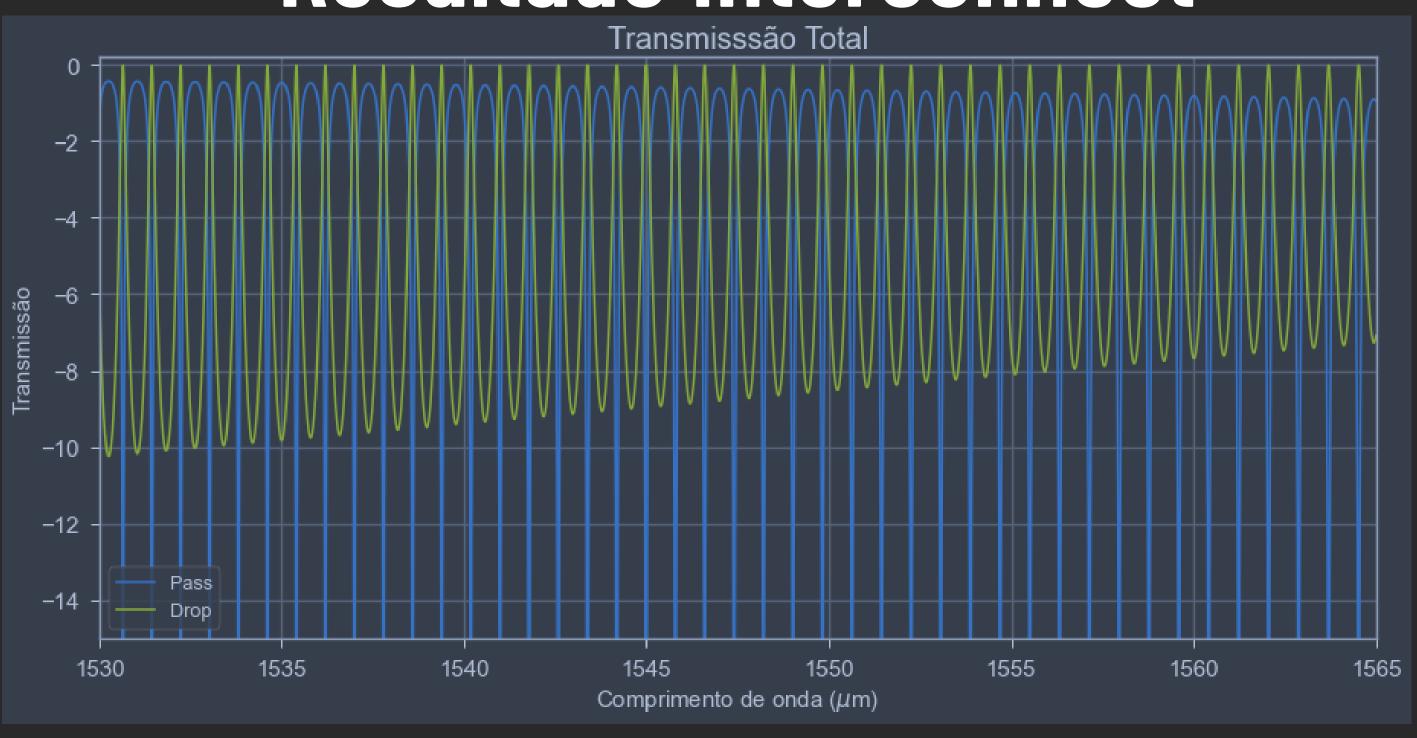


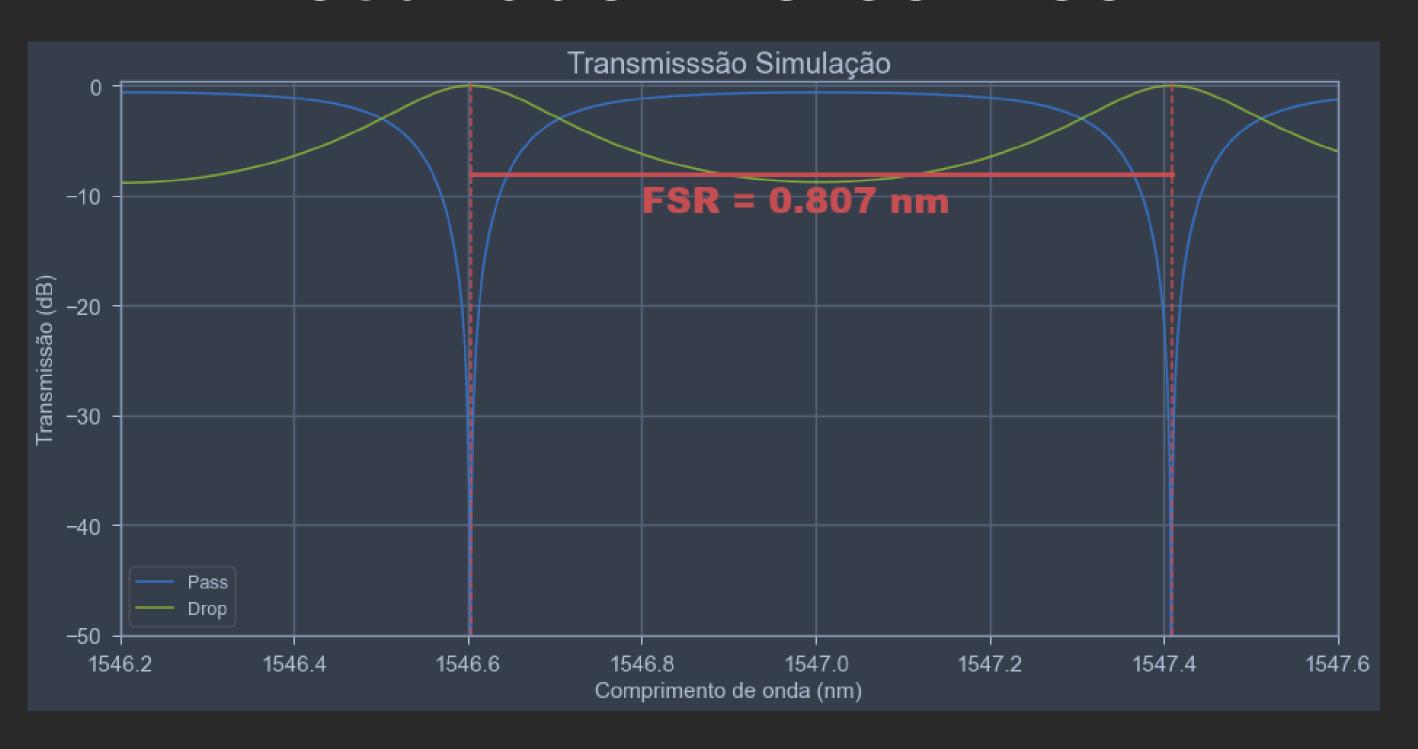


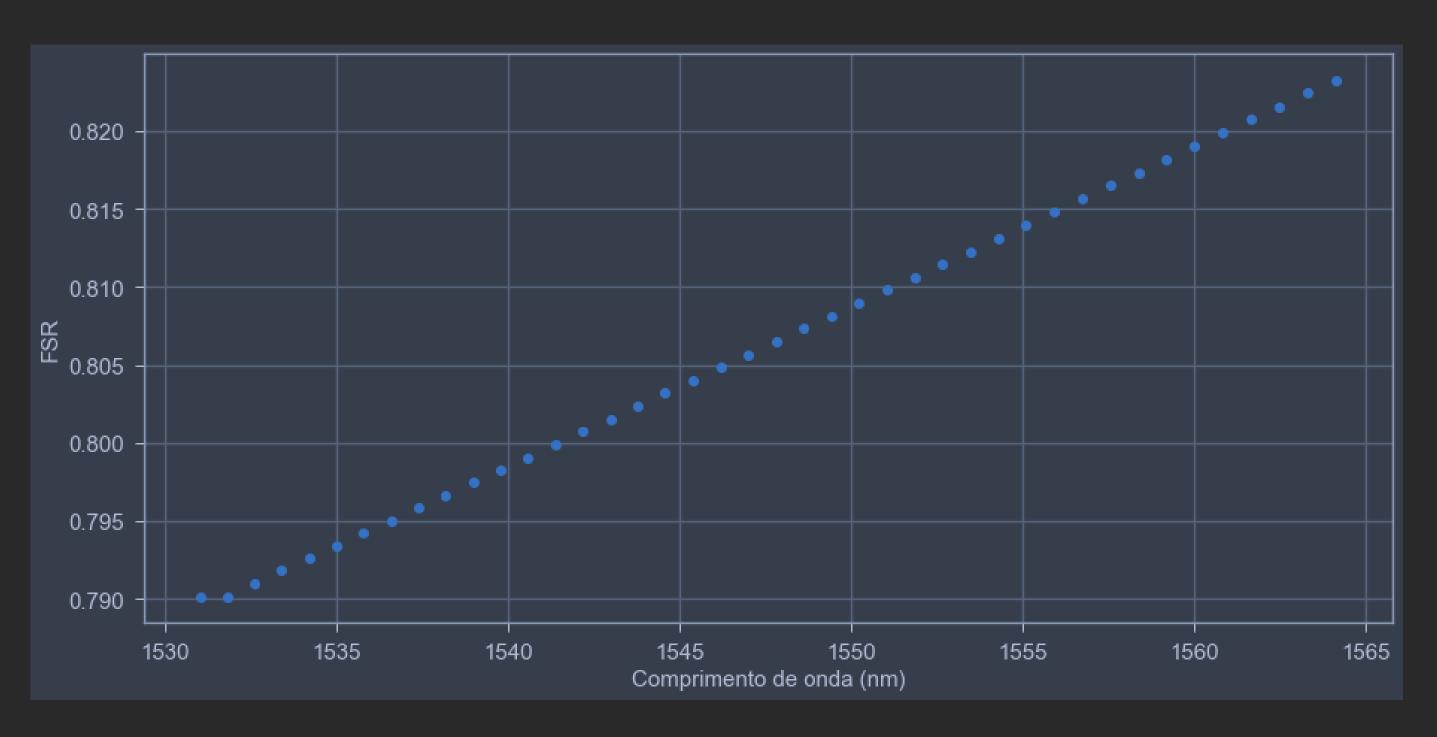


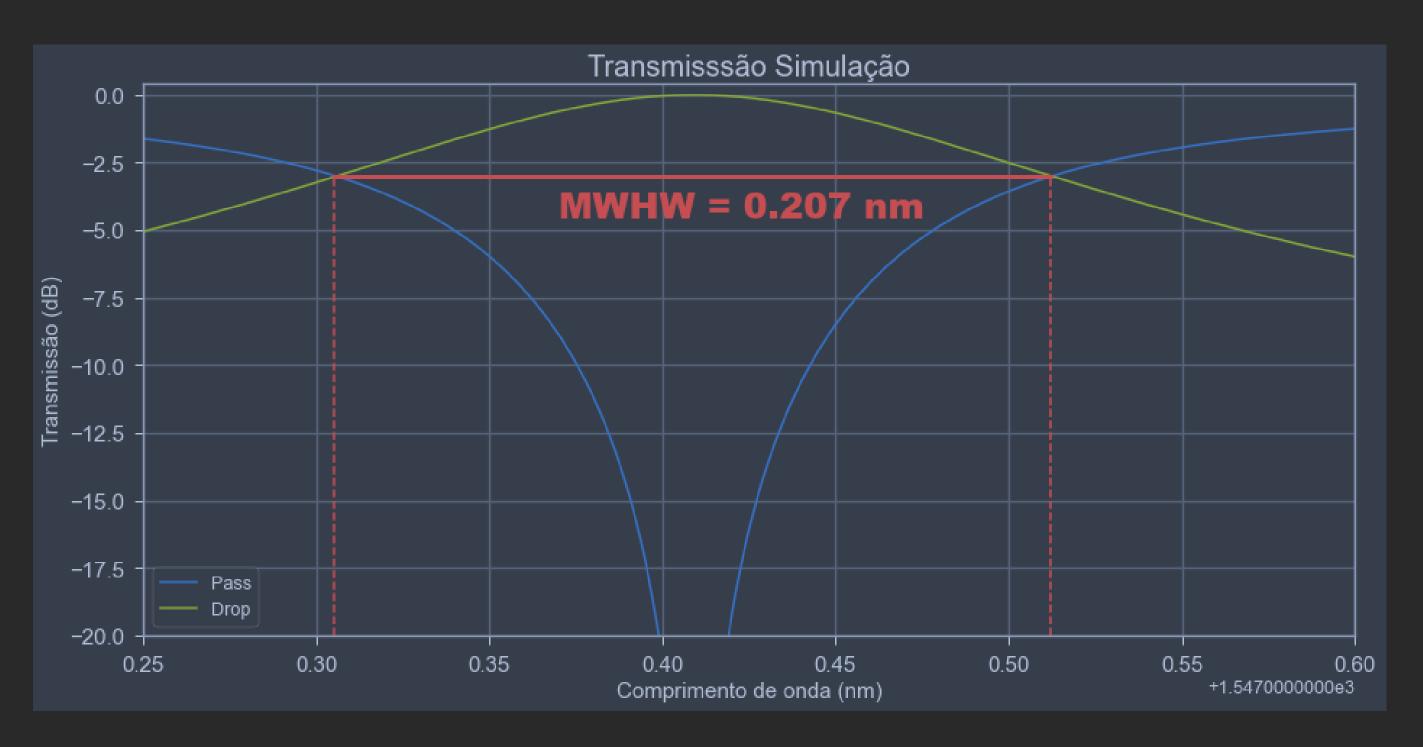
Circuito final

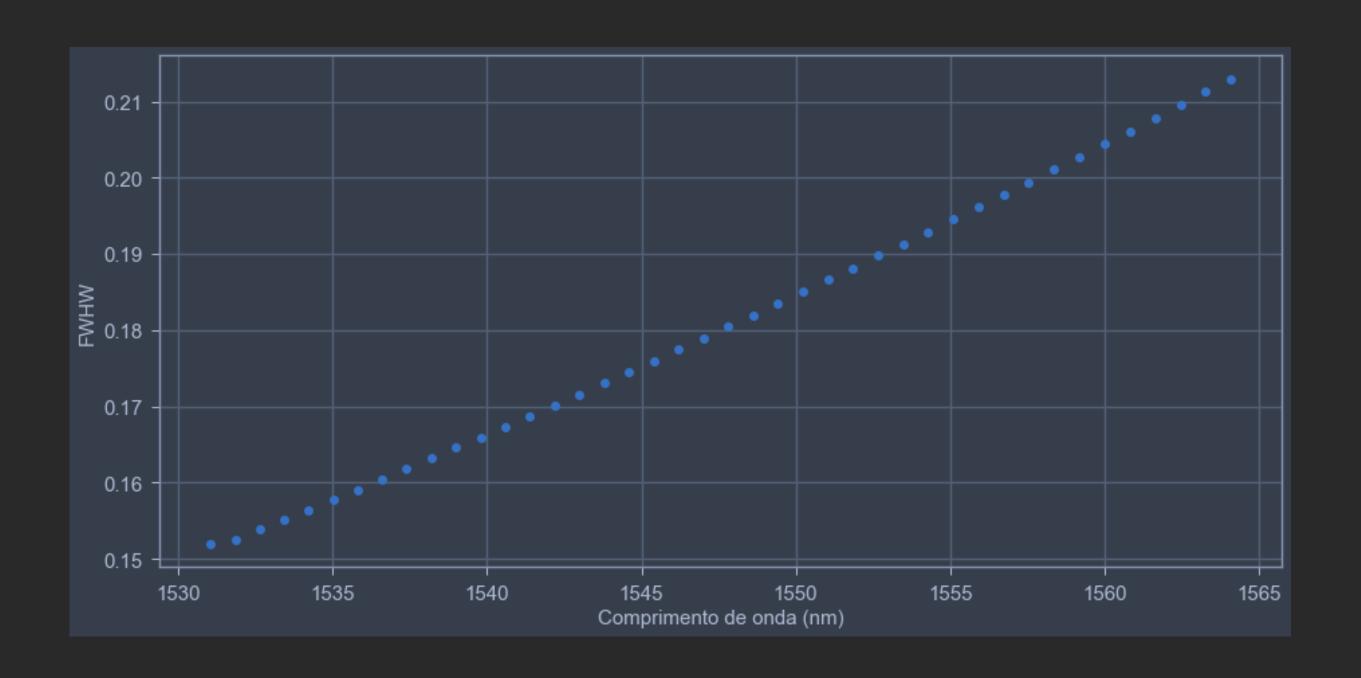


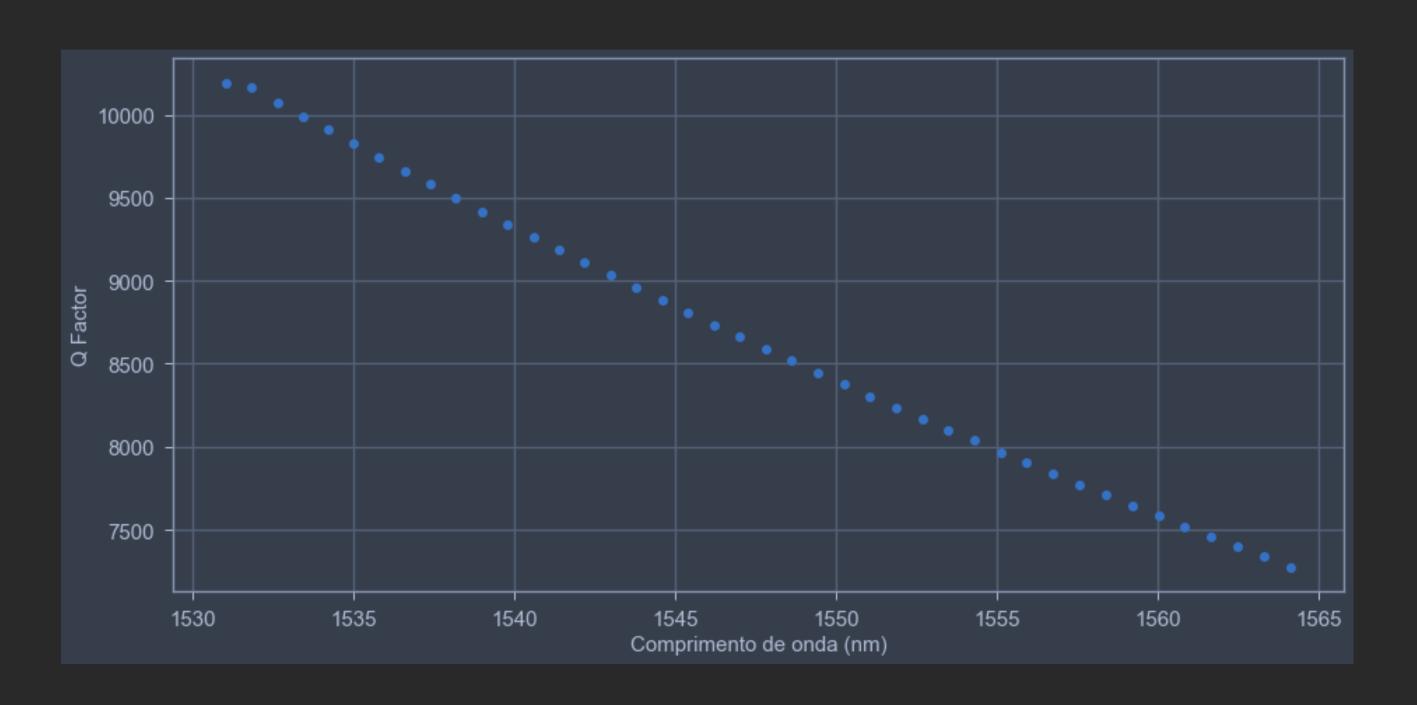


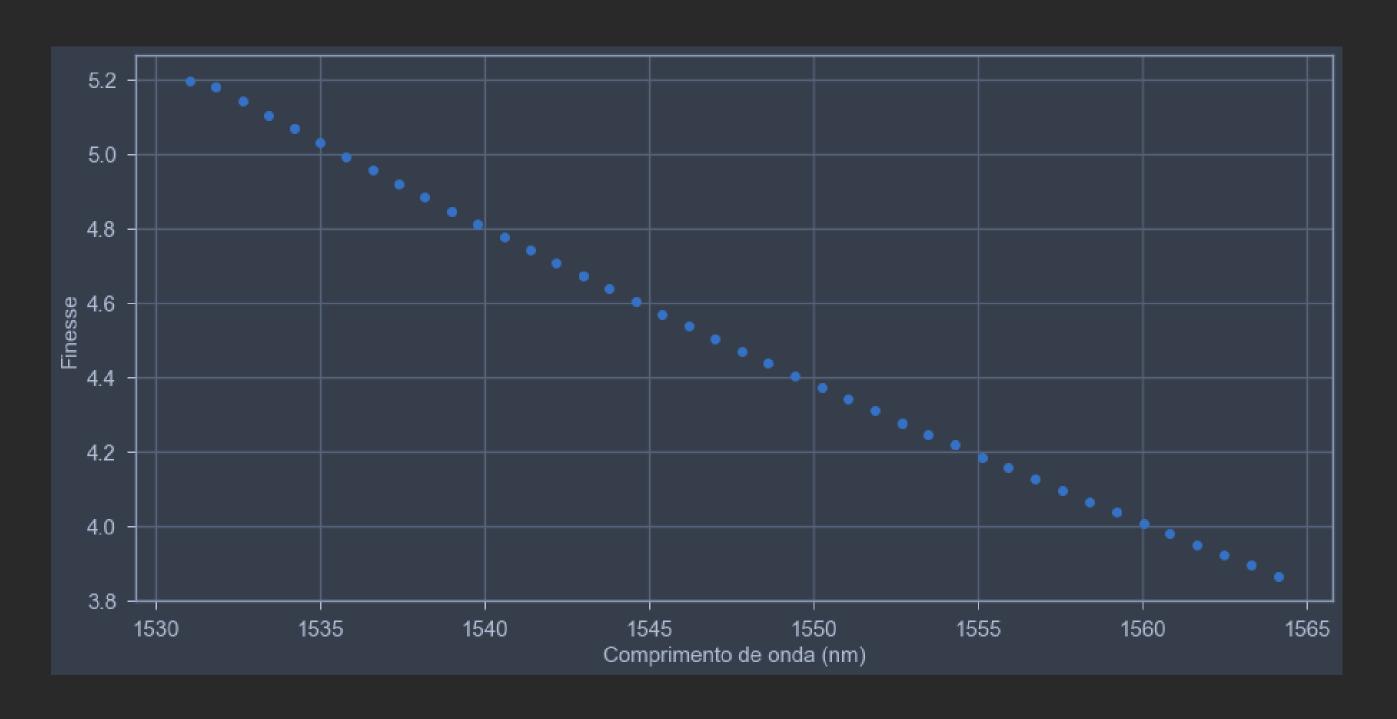








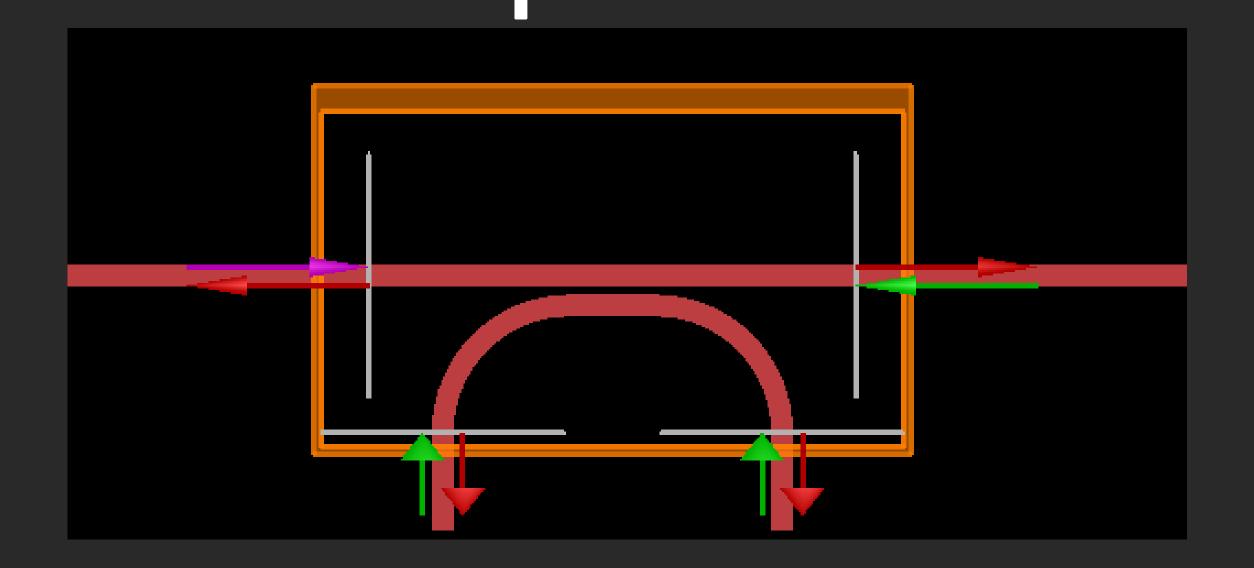


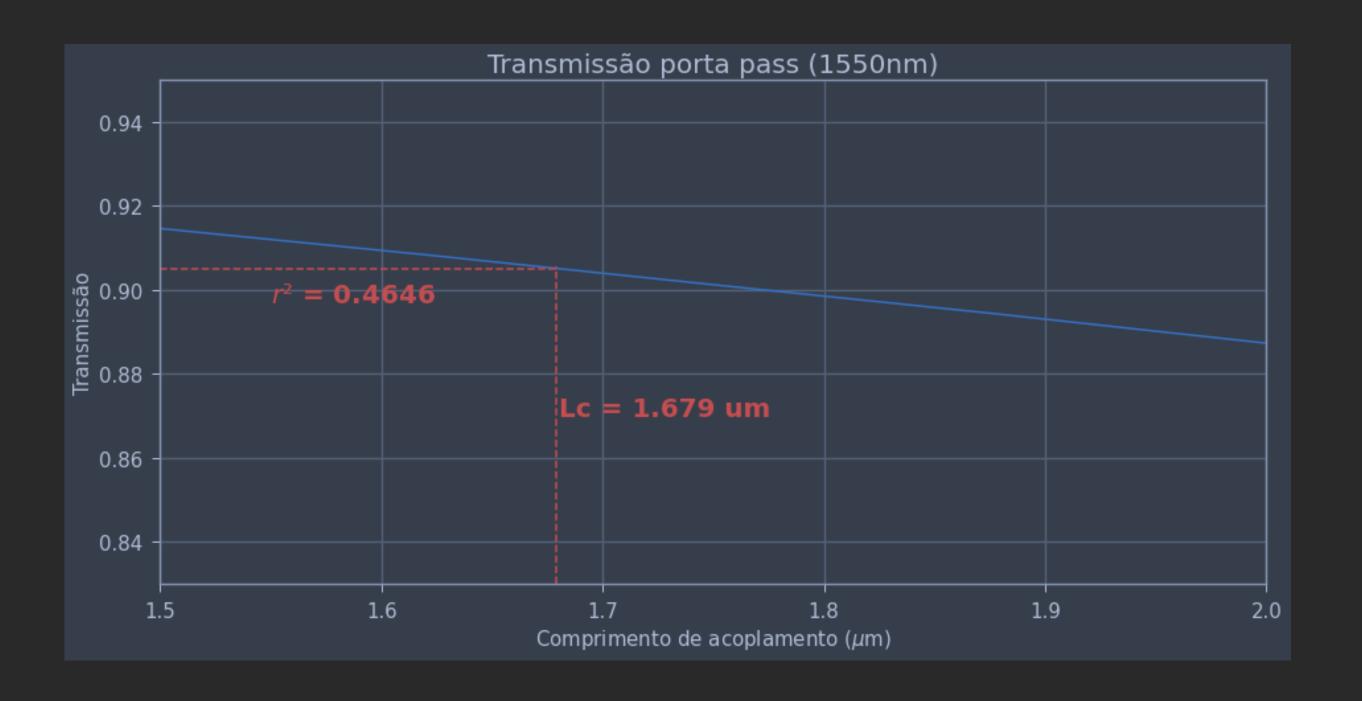


SEMANA 5

Otimização do 1º modelo

DESIGN DE UM ANEL DE RESSONÂNCIA Segunda otimização Chip buried

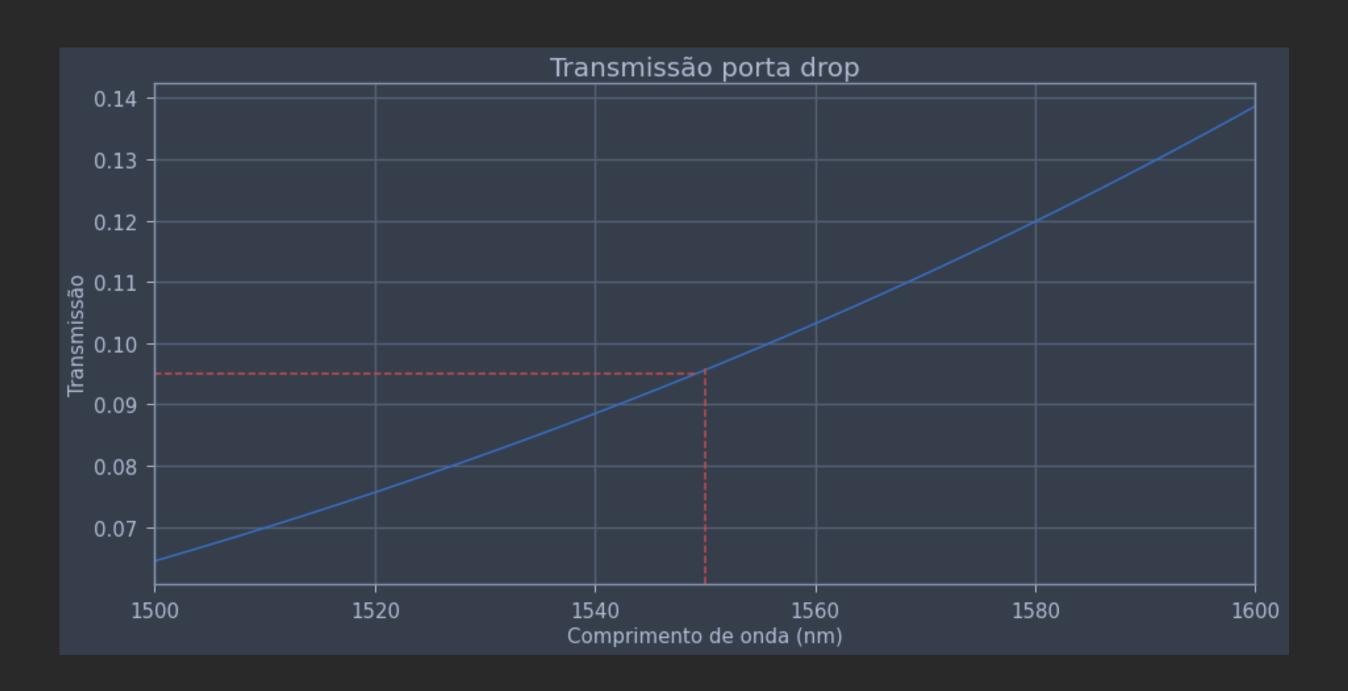




DESIGN DE UM ANEL DE RESSONÂNCIA Simulação FDTD otimizada



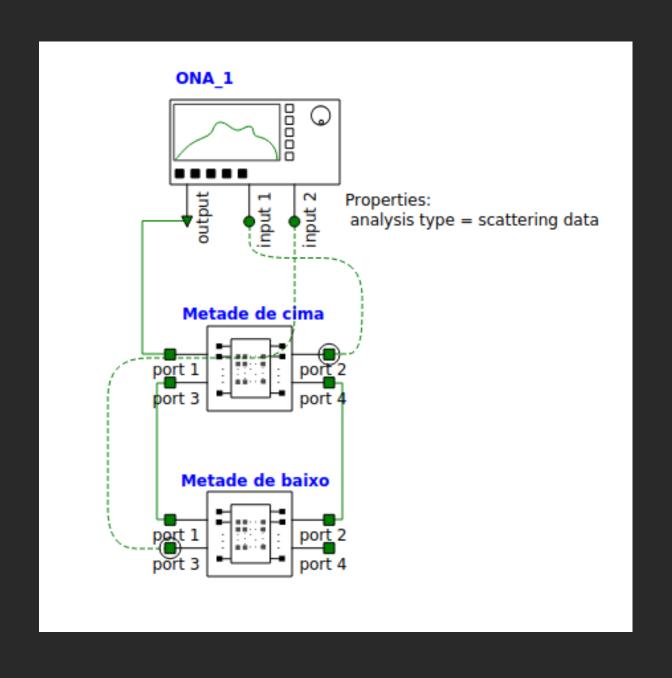
DESIGN DE UM ANEL DE RESSONÂNCIA Simulação FDTD otimizada



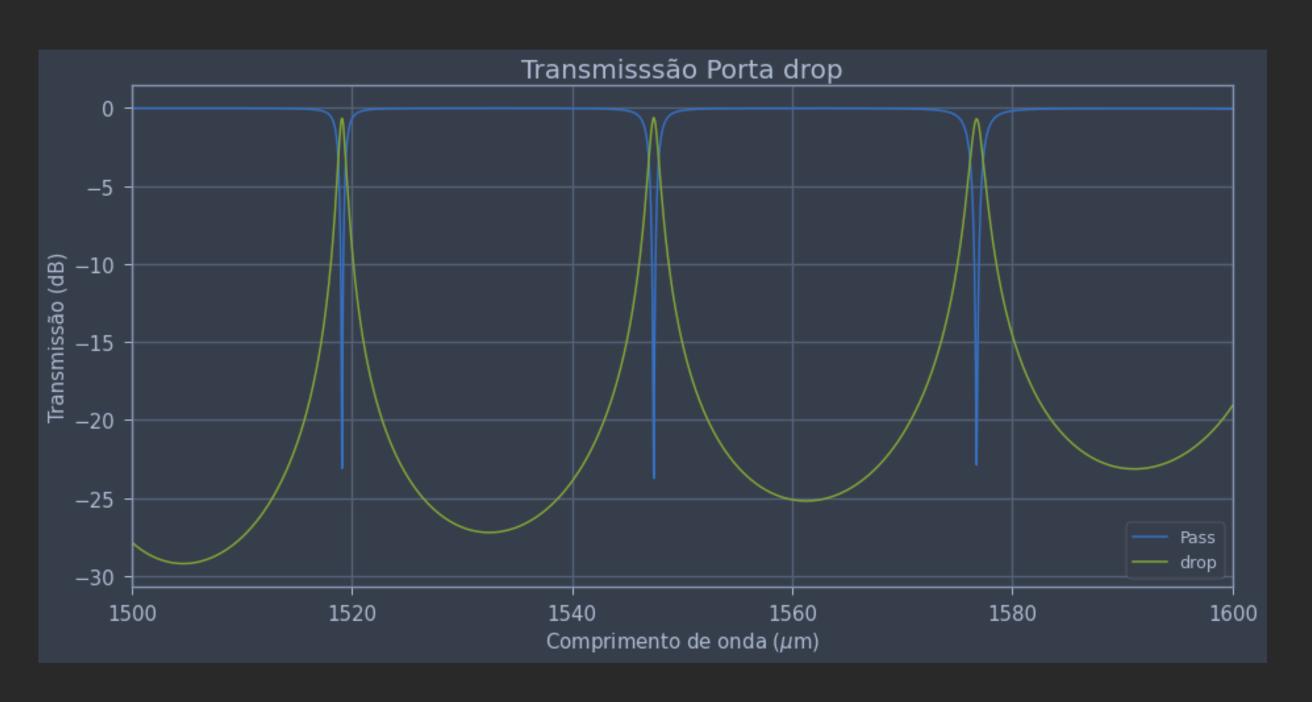
DESIGN DE UM ANEL DE RESSONÂNCIA Simulação FDTD otimizada



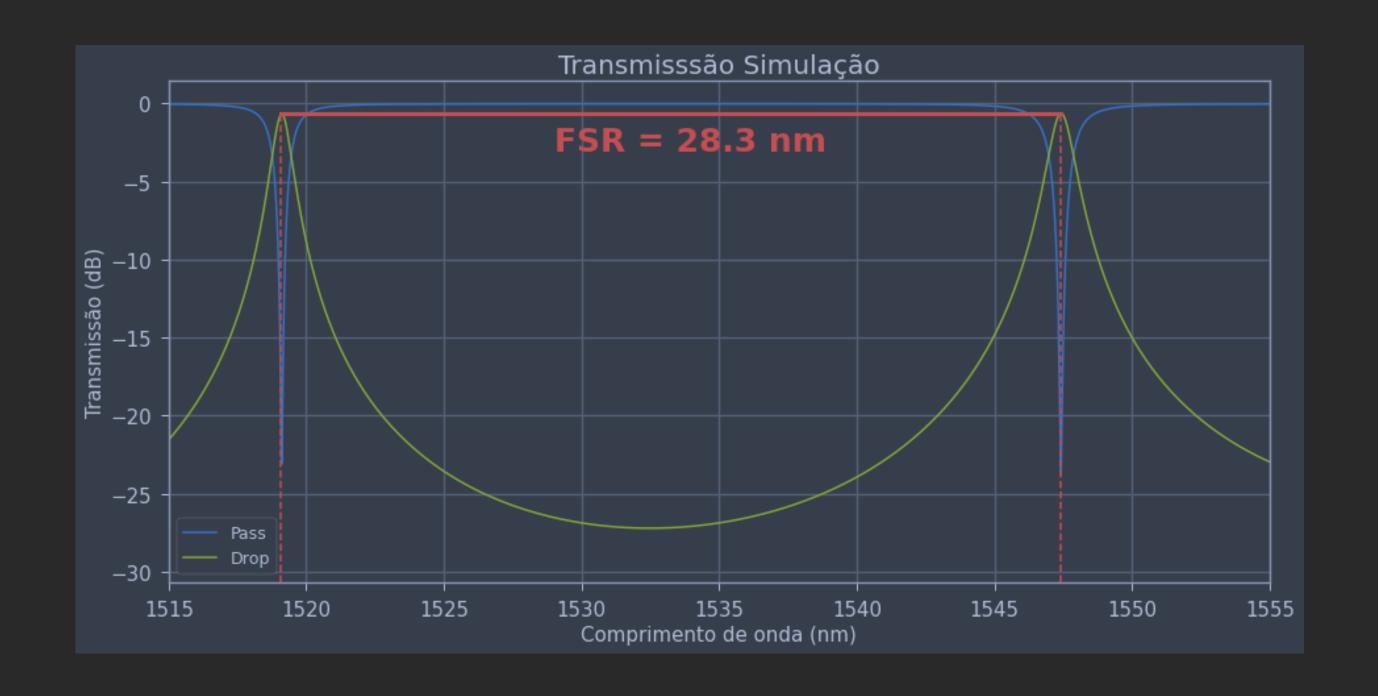
DESIGN DE UM ANEL DE RESSONÂNCIA Export Interconnect

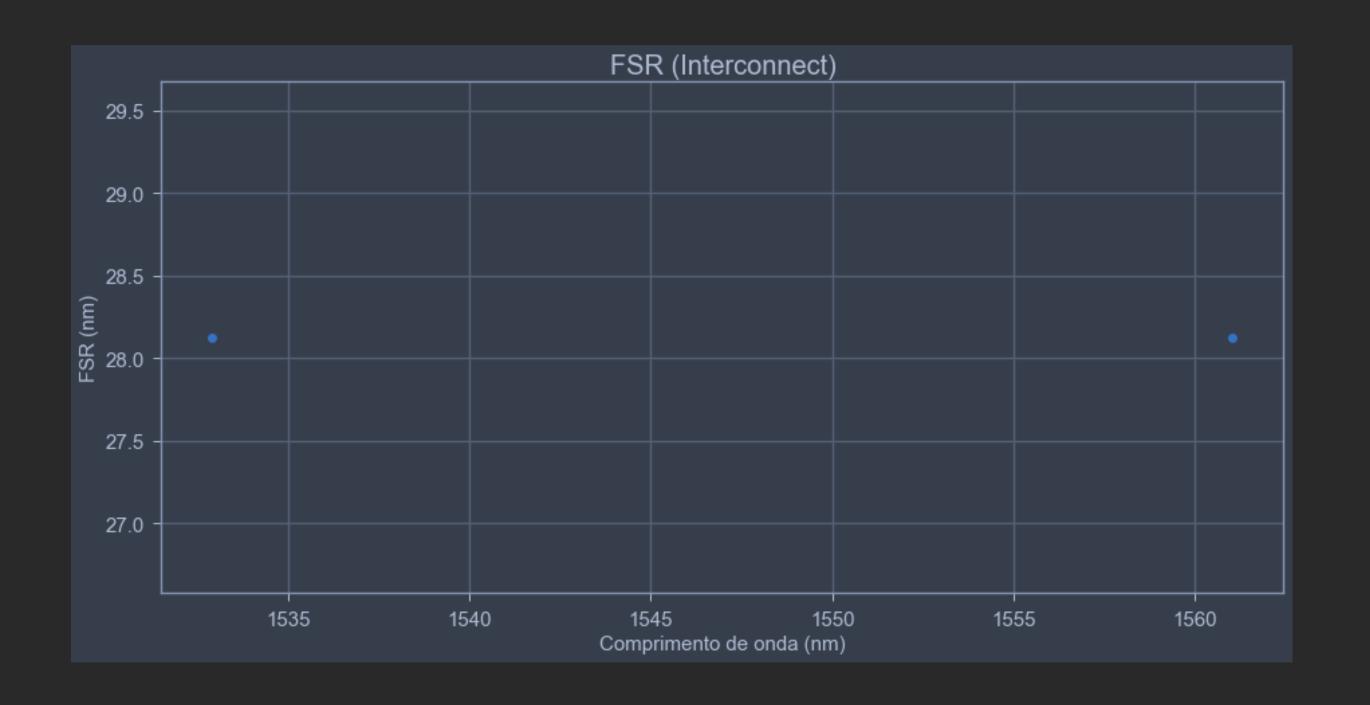


Resultados

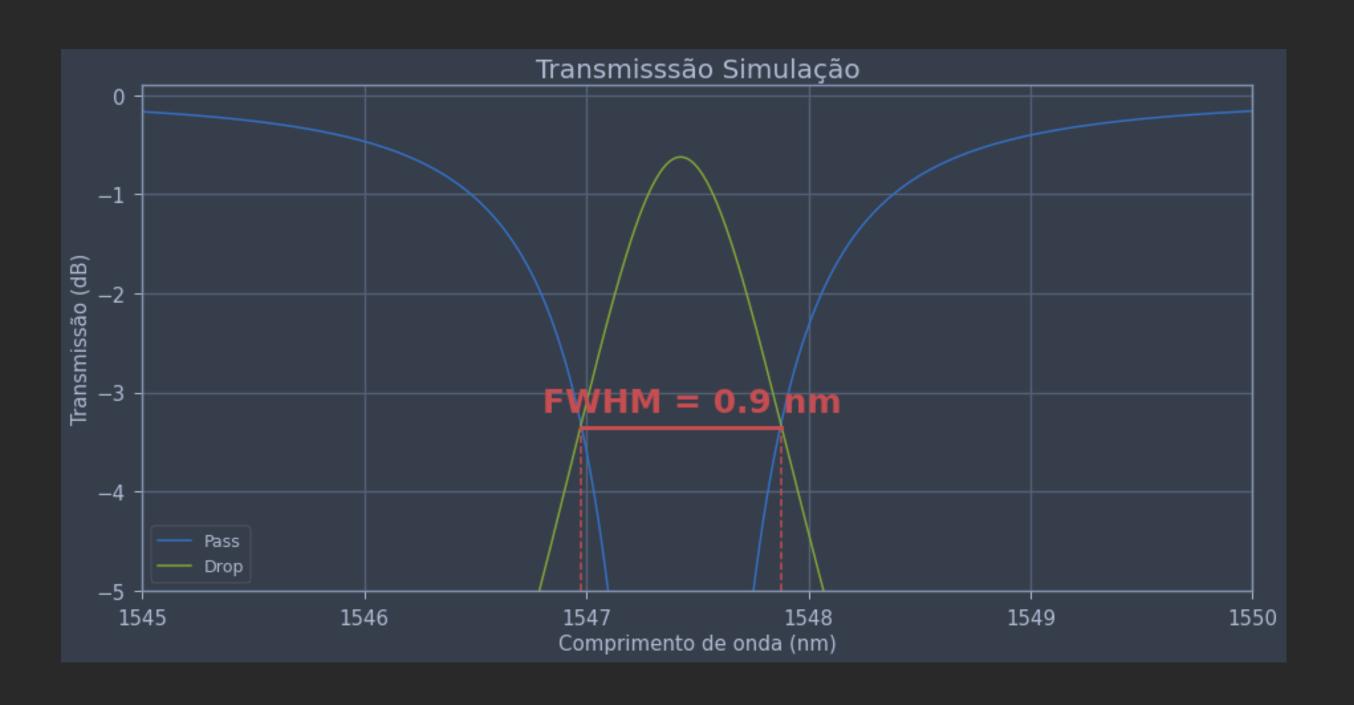








Resultados





Resultados finais do modelo 1

Teorico

FSR = 27.7 nm

MWHW = 0.88 nm

Finesse = 31.48

Q factor = 1761

SOI in SiO2

Obtido

FSR = 28.3 nm

MWHW = 0.9 nm

Finesse = 31.44

Q factor = 1722

Buried in Si02